

# MALTA: an asynchronous readout CMOS monolithic pixel detector for the ATLAS High-Luminosity upgrade.

Roberto Cardella, Lluís Simon Argemi, Ivan Berdalovic, Florian Dachs, Valerio Dao, Leyre Flores Sanz De Acedo, Francesco Piro, Tomasz Hemperek, Bojan Hiti, Thanushan Kugathasan, Cesar Augusto Marin Tobon, Konstantinos Moustakas, Ruth Magdalena Munker, Heinz Pernegger, Petra Riedler, Enrico Junior Schioppa, Abhishek Sharma, Walter Snoeys, Carlos Solans Sanchez, Tianyang Wang, Norbert Wermes, Piotr Rymaszewski, Ignacio Asensi Tortajada

## 1. CMOS development for ATLAS ITk

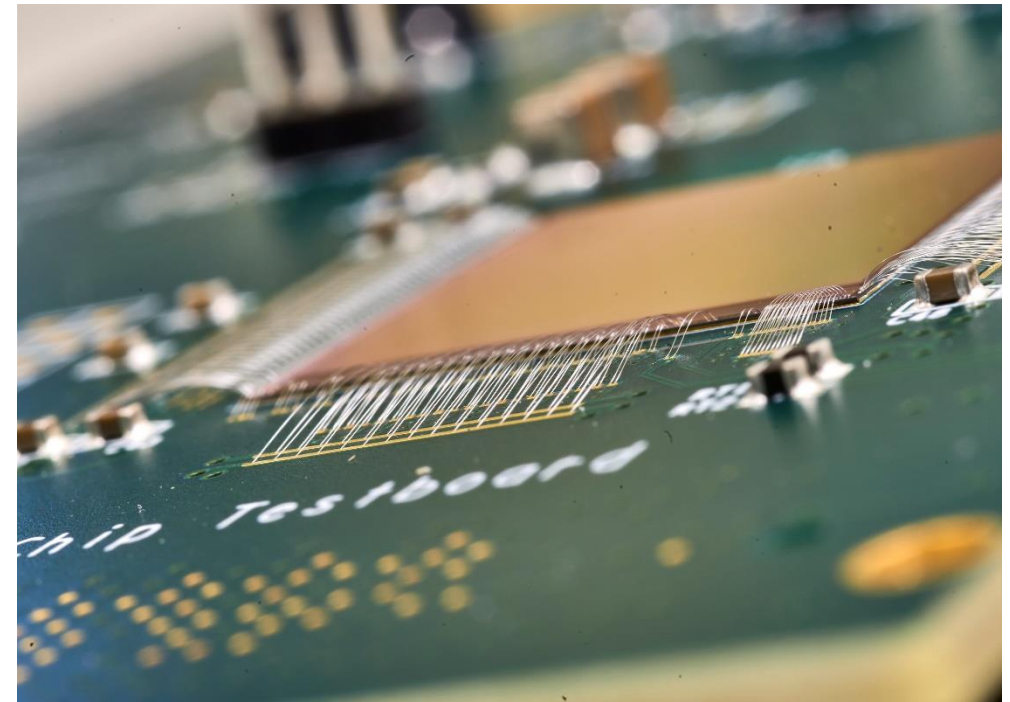
- TowerJazz 180nm technology

## 2. MALTA chip

- Datapath: From the pixel to the output
- Measurements results
- Module design

## 3. Parallel R&D on MALTA

## 4. Conclusions



## Outermost layer of ITk Pixel Barrel

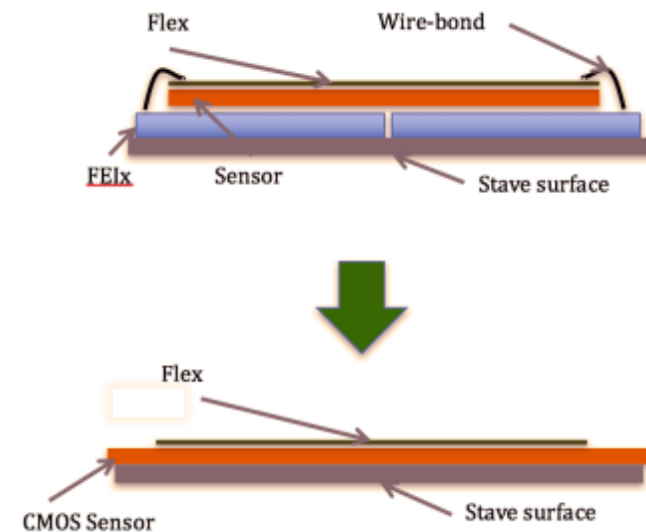
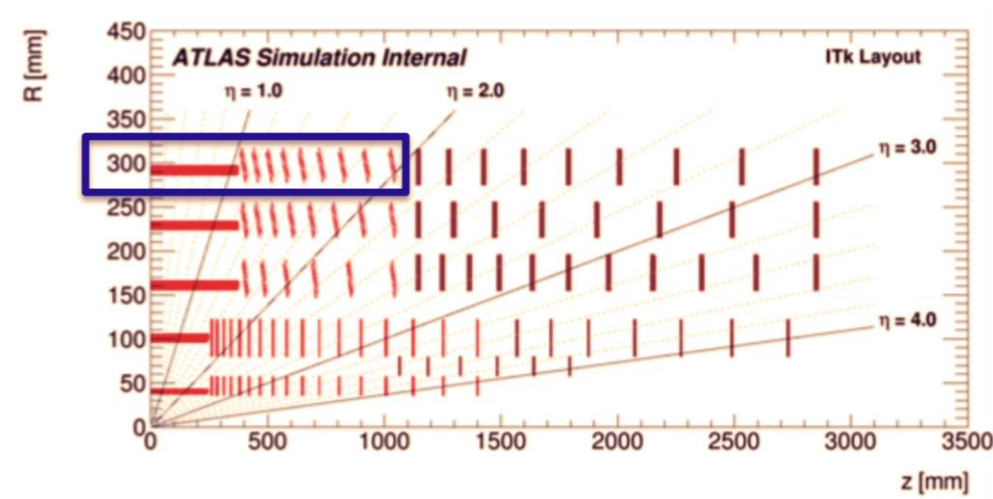
- 2016 quad modules
- 3m<sup>2</sup> (~45% of outer barrel layers)

## For 4000 fb-1 integrated luminosity

- TID = 80Mrad
- NIEL 1.5 x 10<sup>15</sup> neq/cm<sup>2</sup>

## Monolithic CMOS sensors are considered as option for the outermost layer

- Saves bump bonding for ~45% of outer barrel system
- Substantial cost reduction and reduced module assembly time
- Requires “Drop-In” module compatibility to hybrid module

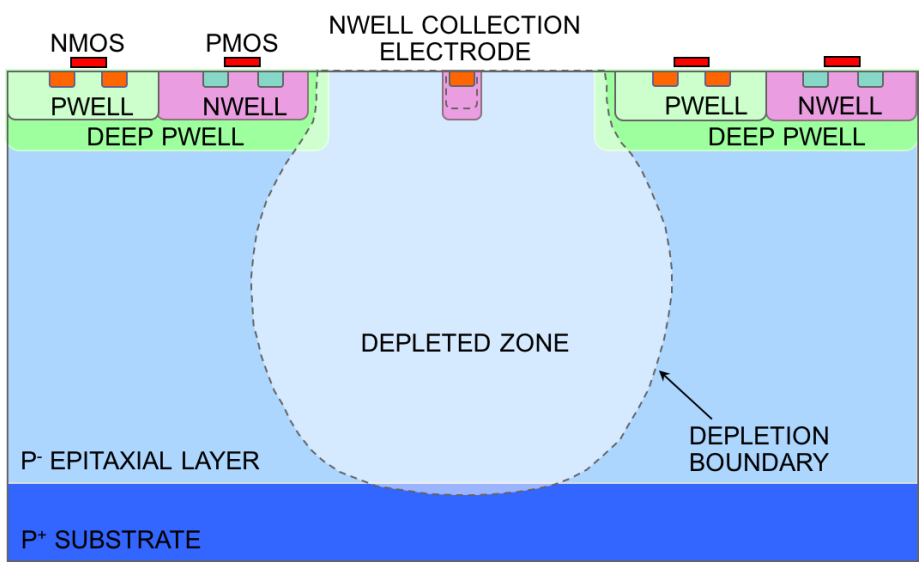


## Standard Process

**Small collection electrode** design with high resistivity ( $> 1 \text{ k}\Omega \text{ cm}$ ) p-type epitaxial layer ( $25 \mu\text{m} \rightarrow \text{MIP} \sim 1500 \text{ e}^-$ )

Deep p-well shielding n-well to allow **full CMOS**

**Reverse bias** ( $\sim 6 \text{ V}$ ): reduce input capacitance and increase depletion volume

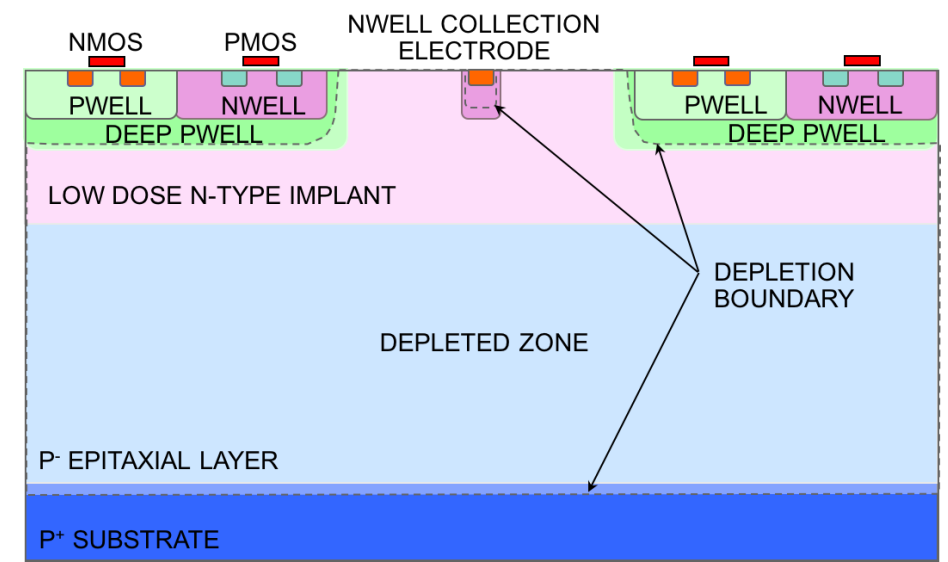


## Modified Process

Adding a **planar n-type layer** to improve depletion under the deep p-well near the pixel edges

A fully depleted epitaxial layer results in faster charge collection and **better radiation tolerance**

No circuit or layout changes required



W. Snoeys et al. <https://doi.org/10.1016/j.nima.2017.07.046>

## Standard Process

## Modified Process

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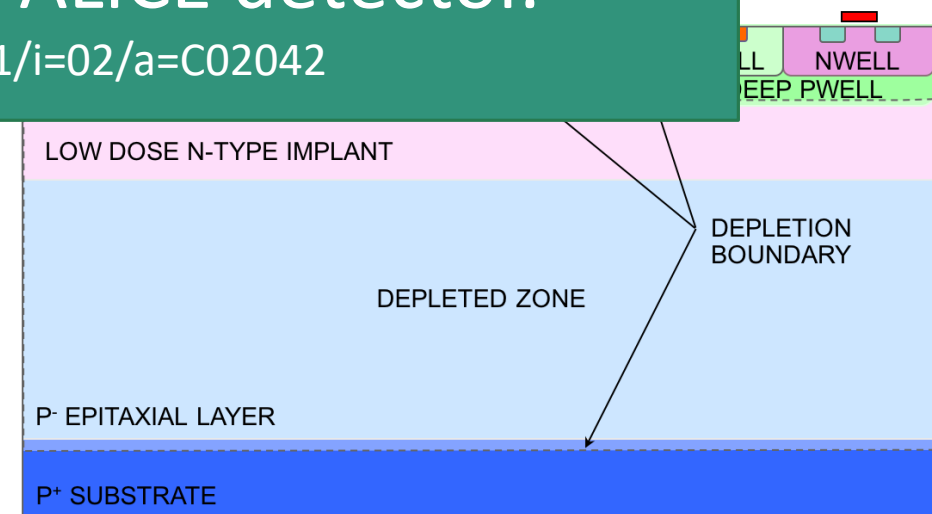
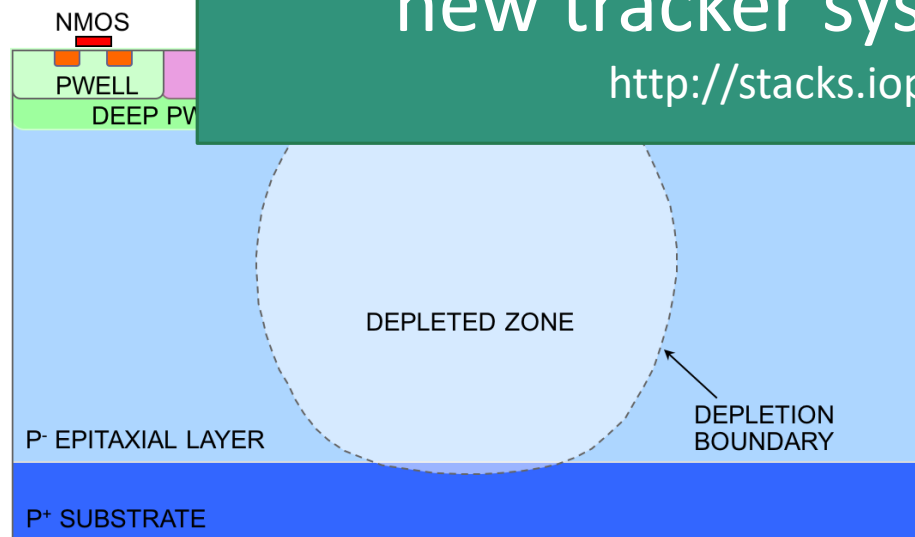
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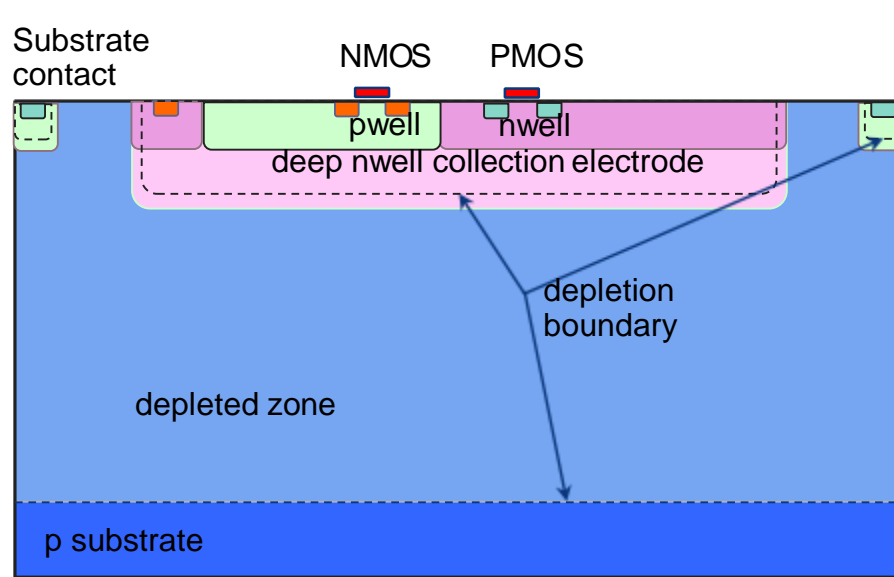
Deep p-well shielding n-well to allow **full CMOS**

A fully depleted epitaxial layer results in faster charge collection and **better radiation tolerance**

**Reverse bias**  
increase depl

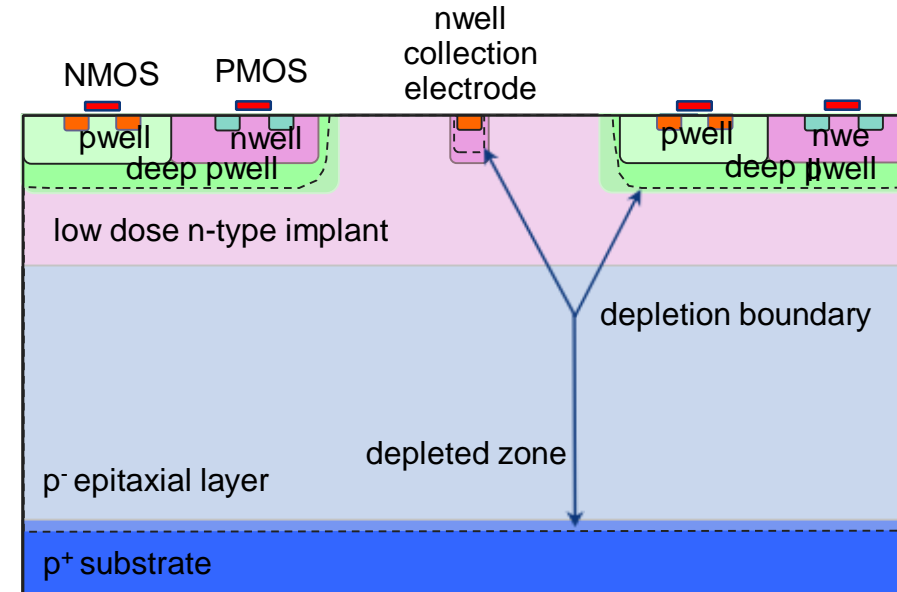
**ALPIDE (standard process) will be installed in the new tracker system of the ALICE detector.**  
<http://stacks.iop.org/1748-0221/11/i=02/a=C02042>





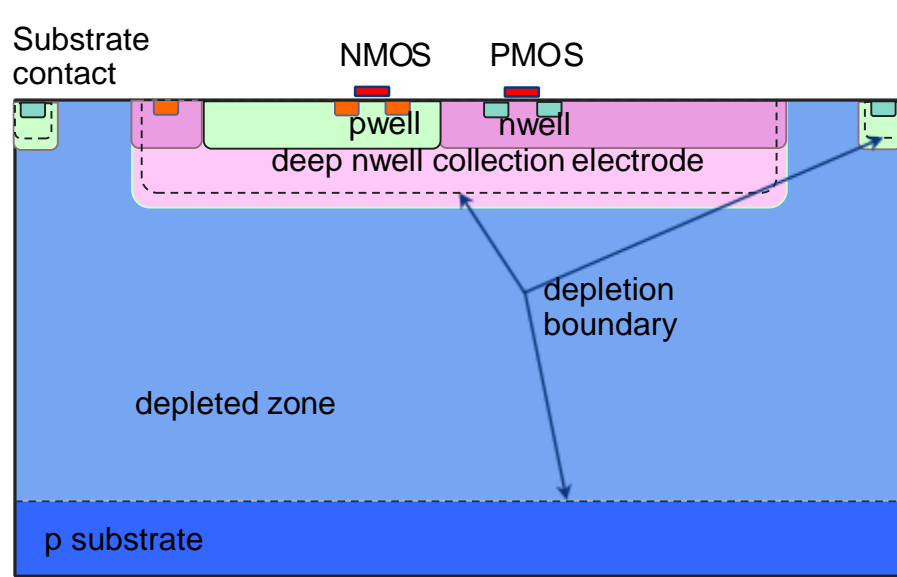
## Large collection electrode (HV-CMOS)

- Large capacitance
- Higher power
- Electronics in the input well, signal coupling
- Practically uniform field
- Very high radiation tolerance

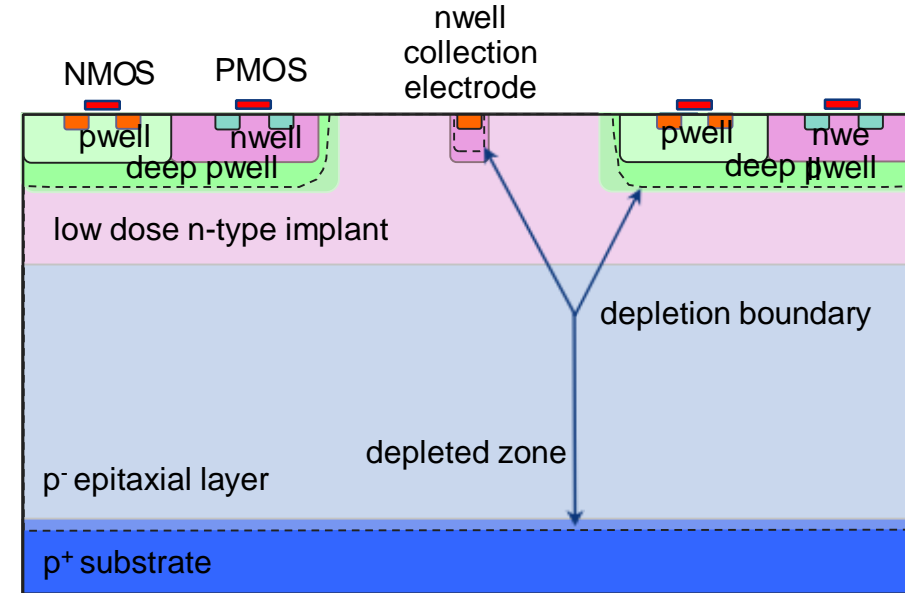


## Small collection electrode (TJ)

- Small capacitance
- Lower power
- Less prone to coupling
- Process modification for full depletion and radiation tolerance increase



Large collection electrode (HV-CMOS)



Small collection electrode (TJ)

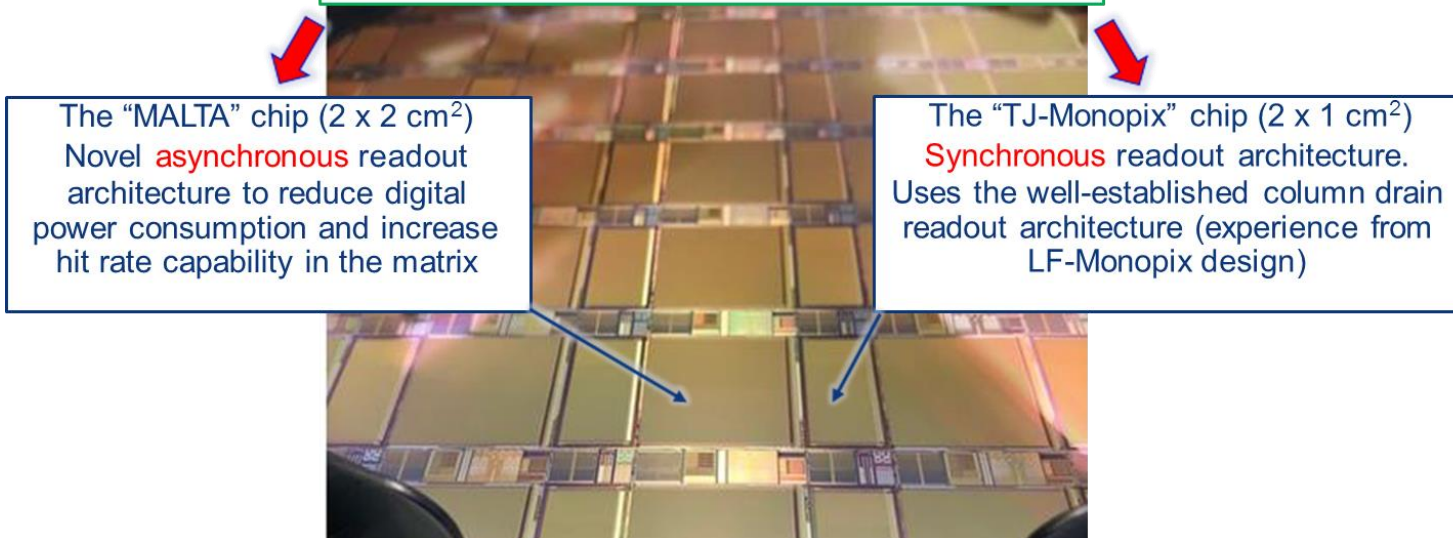
Power/Chip [mW]	TJ Asynch.	TJ Synch.	Large Electr. Synch.
Matrix Analog	238	238	1000
Matrix Digital	12	240	80
Total Expected	514	703	1305

Measurement results show improved non-ionizing radiation tolerance for sensors manufactured using the modified process



Analog front-end optimized for timing, based on ALPIDE

Design of two large scale demonstrators to match ATLAS specifications for outer pixel layers  
Collaboration CERN – Uni. Bonn



The “MALTA” chip (2 x 2 cm<sup>2</sup>)  
Novel **asynchronous** readout architecture to reduce digital power consumption and increase hit rate capability in the matrix

The “TJ-Monopix” chip (2 x 1 cm<sup>2</sup>)  
**Synchronous** readout architecture. Uses the well-established column drain readout architecture (experience from LF-Monopix design)

## Talk on TJ-Monopix

Thu 13/12 12:00 I. D. Caicedo Sierra

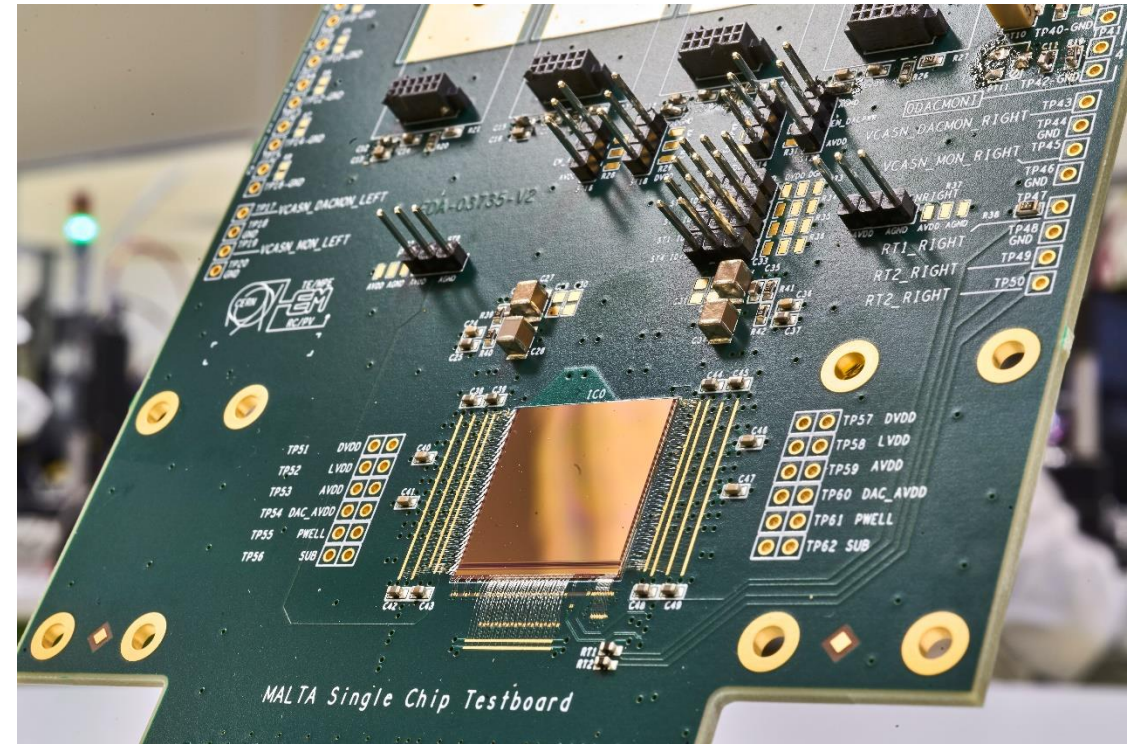
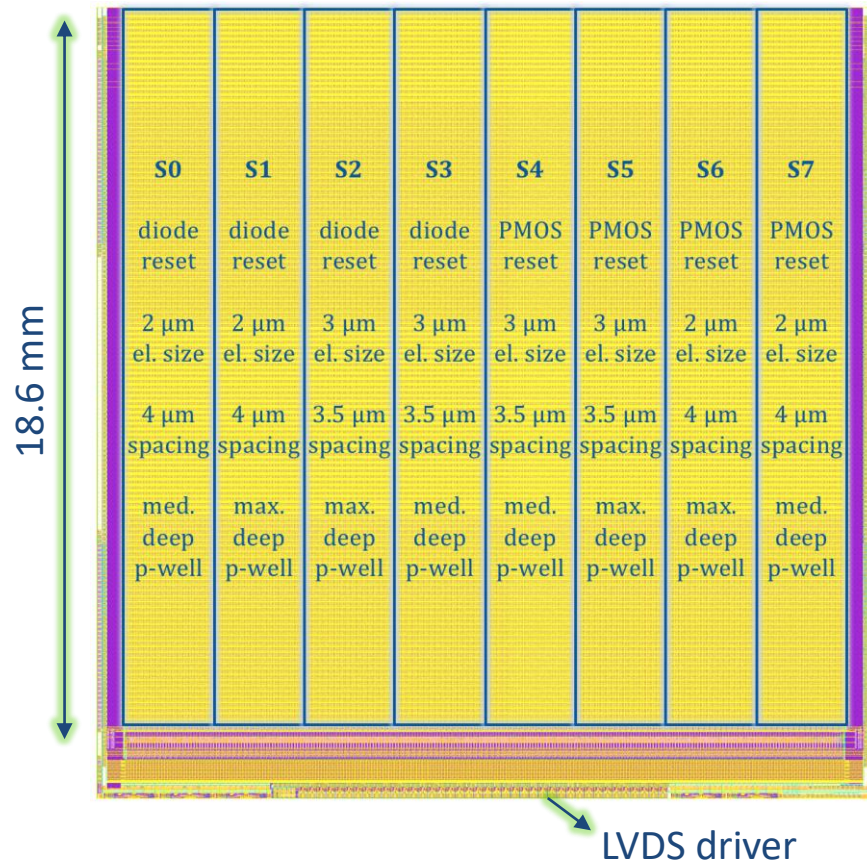
R&D status of the Monopix chips: Depleted monolithic active pixel sensors with a column-drain read-out architecture for the ATLAS Inner Tracker upgrade



The 512x512 pixel - 8 sectors

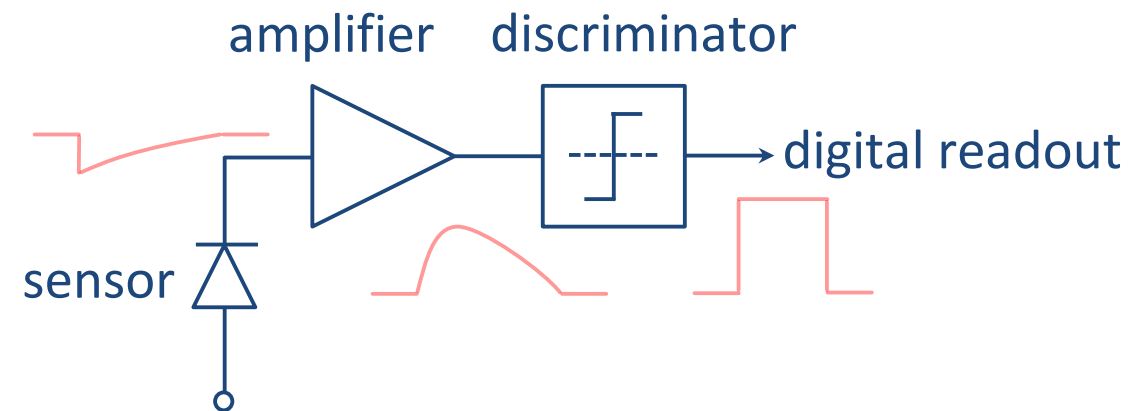
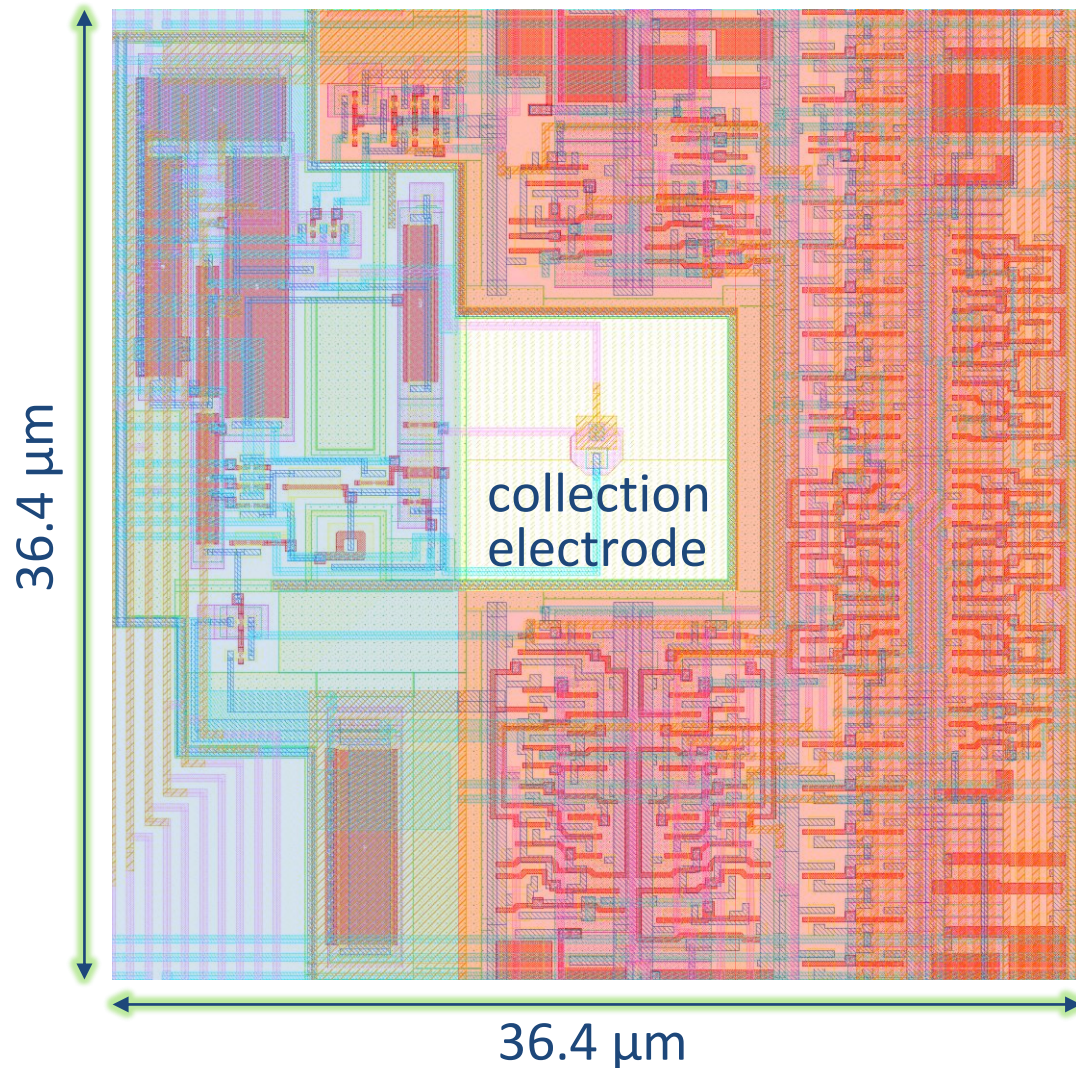
The front-end is a development from the ALPIDE one.

Design based on a **low-power analogue front-end** and a novel **asynchronous architecture** to read out the pixel matrix



analogue

digital

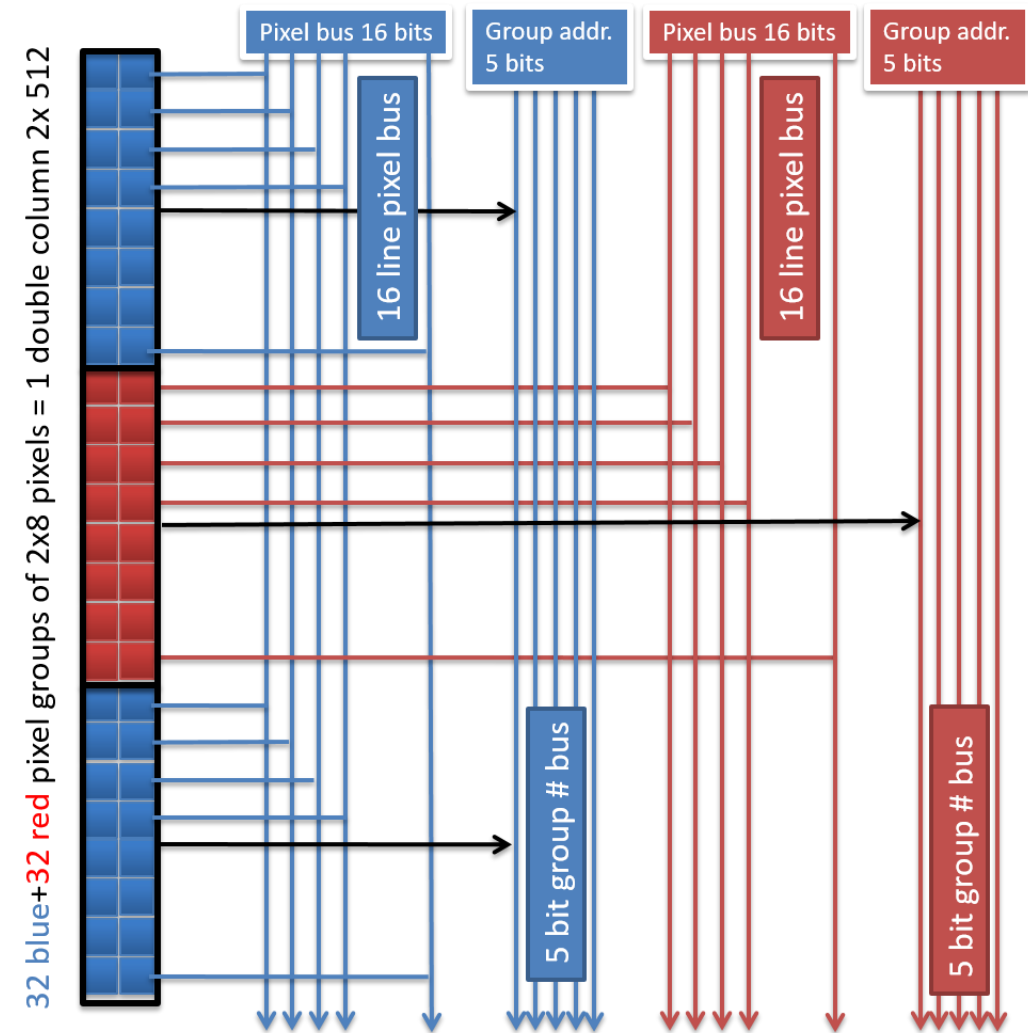


- 2-3  $\mu\text{m}$  collection electrode  $\rightarrow$  small input capacitance
- 3.4 – 4  $\mu\text{m}$  separation between electrode and electronics  $\rightarrow$  low cross talk
- 1  $\mu\text{W}/\text{pixel}$  analog power (75  $\text{mW}/\text{cm}^2$ )
- 10  $\text{mW}/\text{cm}^2$  digital power @ layer4

Sensor and analogue front-end (shaper-amplifier and discriminator) shielded from digital part to **minimise crosstalk**

**Time walk information preserved**

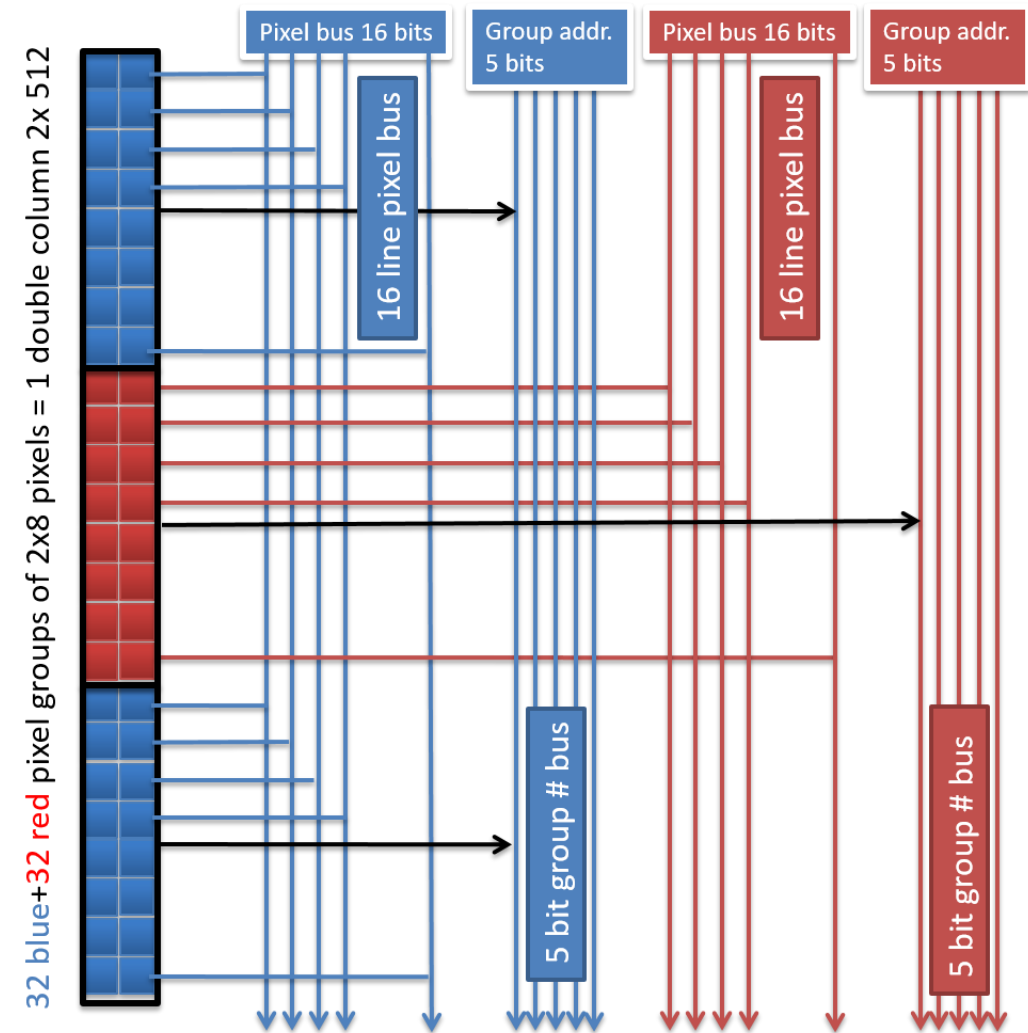
- Front-end output injected into double-column digital readout logic
- Hits are stored using in-pixel flip-flops and transmitted asynchronously over high-speed buses to the end-of-column logic (digital periphery)
- **No clock distribution over the active matrix** – reduces power consumption!
- Double-column divided into groups of 2x8 pixels (“red” and “blue”)
- Buses shared by all groups of the same colour in the double-column, total of 64 groups
- Each hit is hence represented by a 40 bit word, **asynchronously transmitted via parallel LVDS drivers**



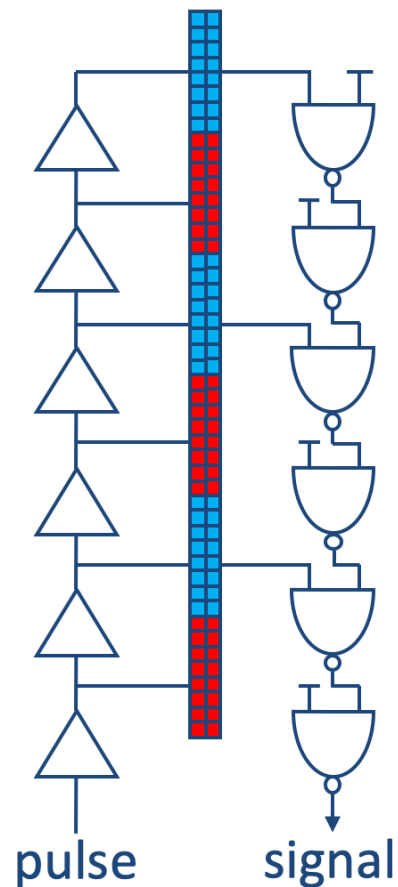
- Front-end output injected into double-column digital readout logic
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- **No clock distribution over the active matrix** – reduces power consumption!

Power/Chip [mW]	TJ Asynchronous	TJ Synchronous
Matrix Analog	238	238
Matrix Digital	12	240
Total Expected	514	703

**Factor 20 for matrix digital power**  
**More than 25% of total power**



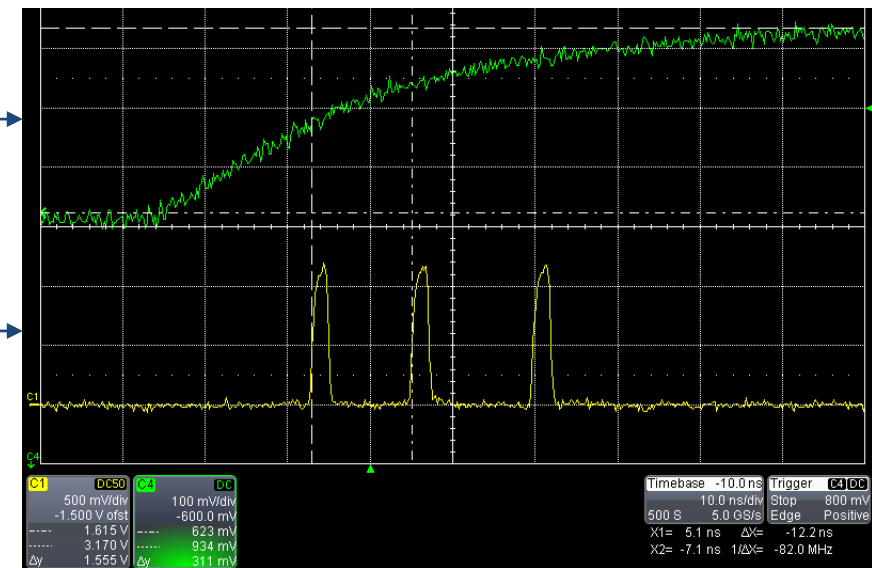
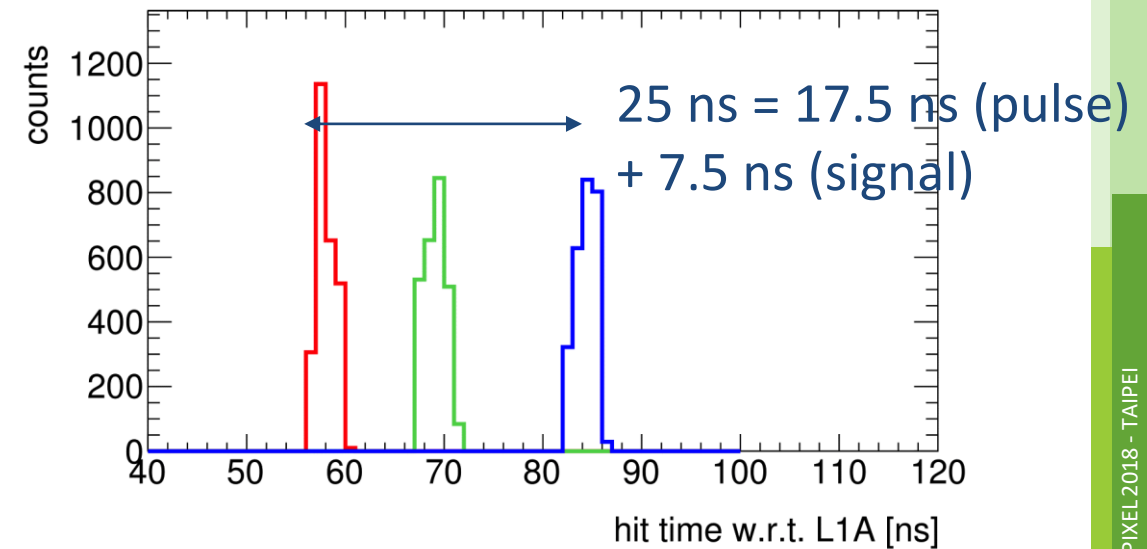
Hit signals from the pixels are buffered and arrive at the end-of-column with a maximum propagation delay of **~7.5 ns**



(measured by pulsing pixels on top, middle and bottom of the column)

analogue output of one pulsed pixel

reference signal

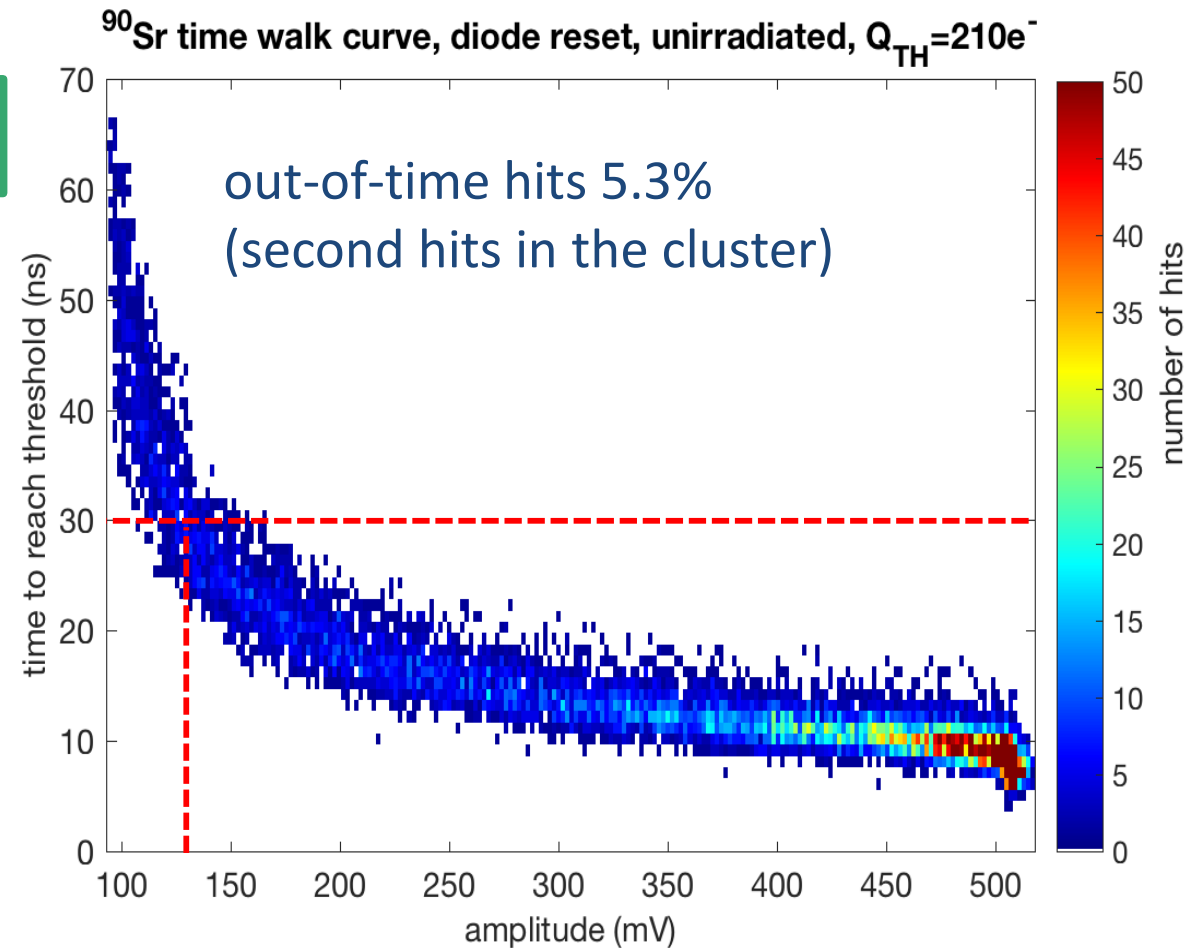


	Outer Layer	Inner Layer
Required Time Res. [ns]	25	25
Particle Rate [MHz/mm <sup>2</sup> ]	1	30
Fluence [n <sub>eq</sub> /cm <sup>2</sup> ]	10 <sup>15</sup>	10 <sup>16</sup>
Ion. Dose [Mrad]	50	1000

Time walk measurement performed with a <sup>90</sup>Sr source using special pixels to monitor the analogue output

With a threshold of 210 e<sup>-</sup> the **in-time threshold** is **300 e<sup>-</sup>** (20% of MIP charge)

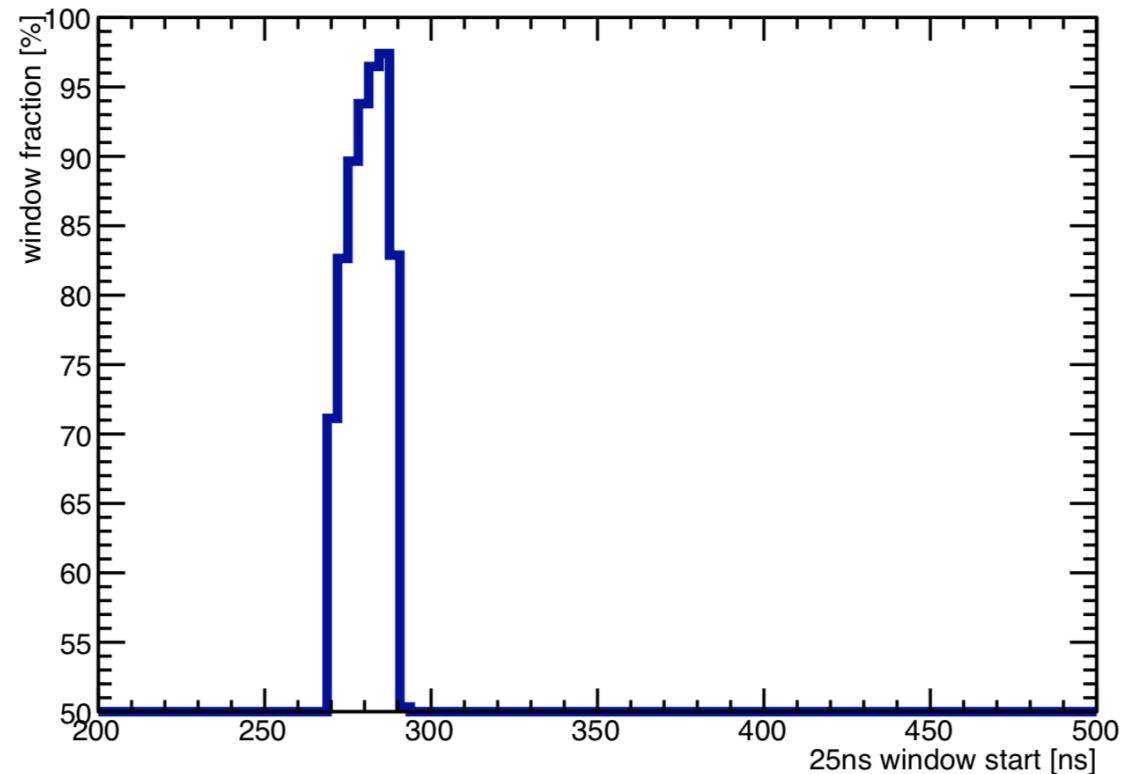
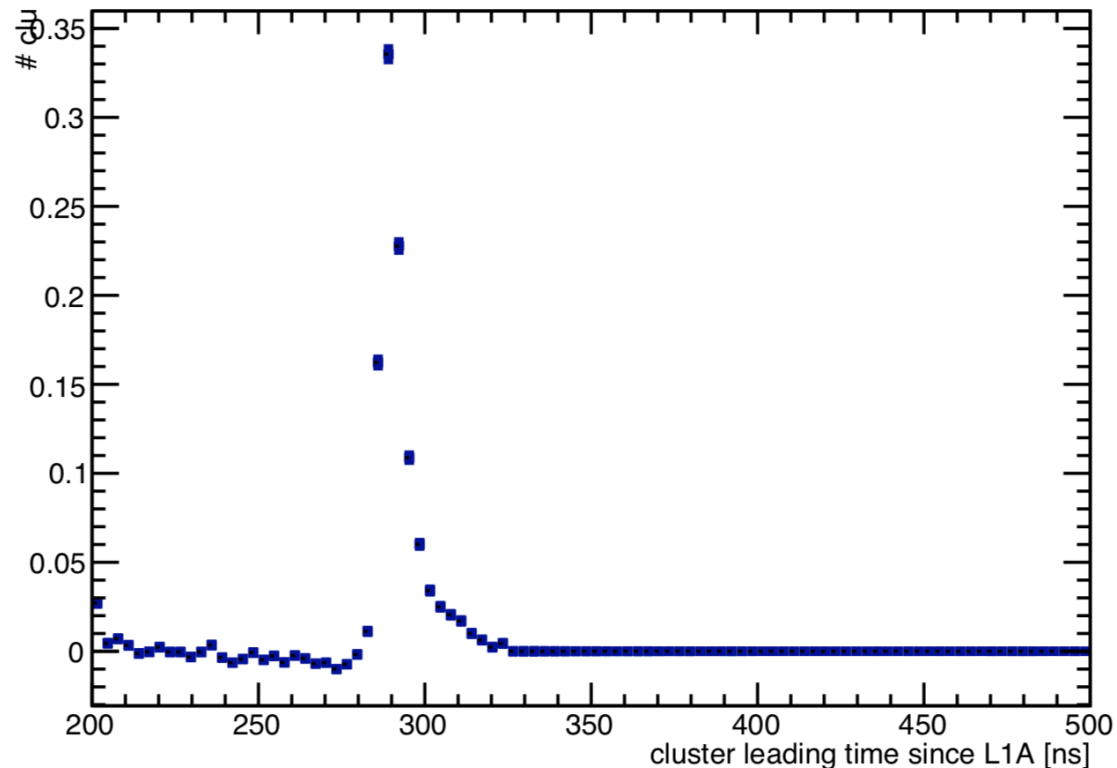
**Out-of-time hits due to charge sharing**  
(measurement done on a single pixel)

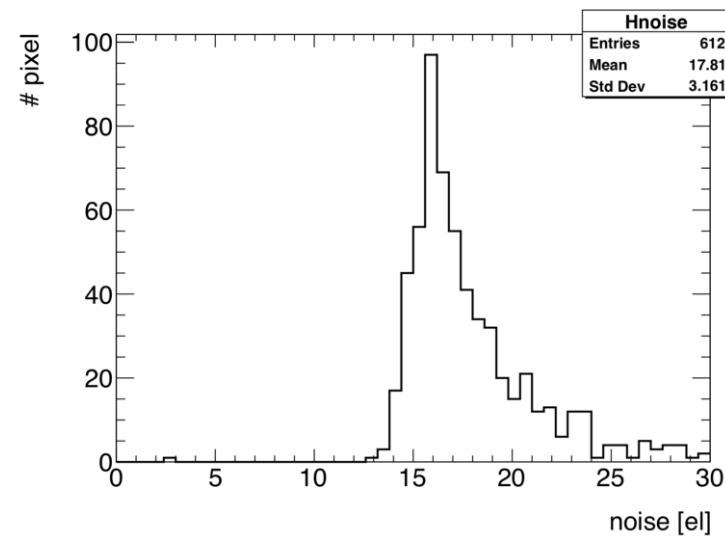
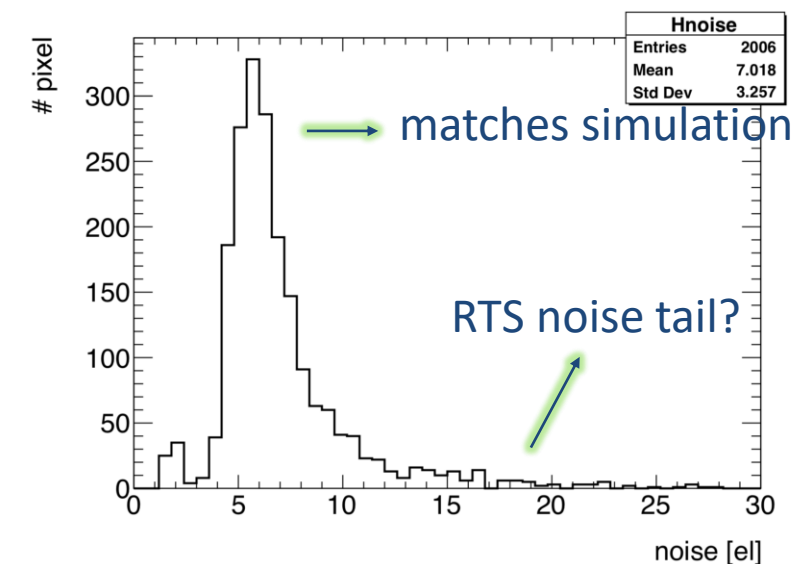
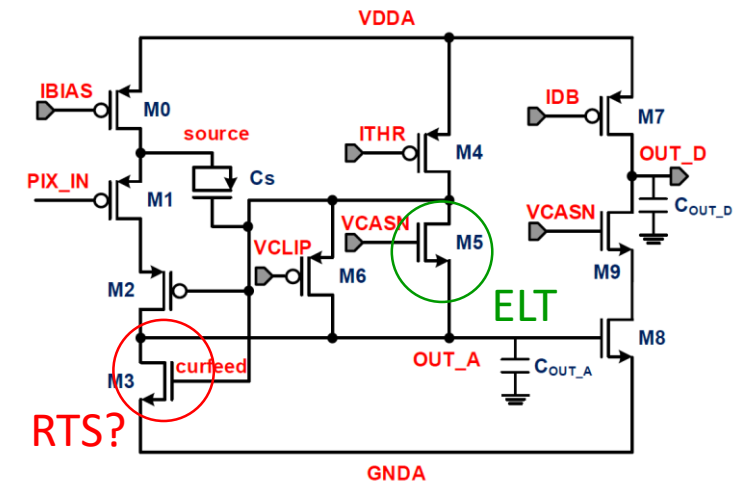
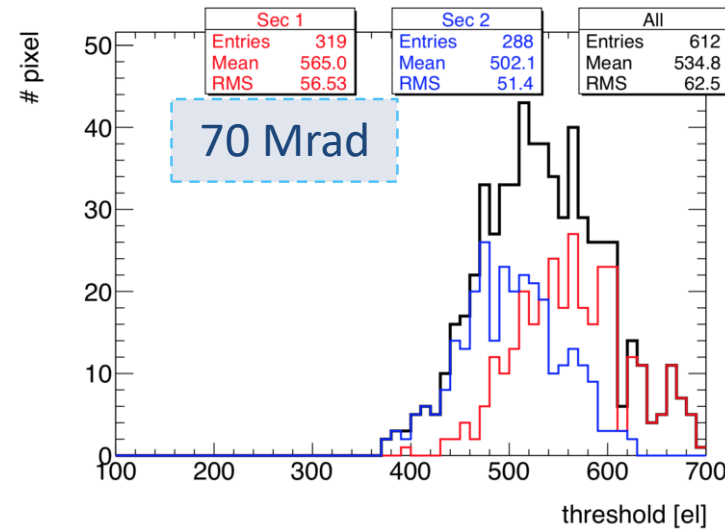
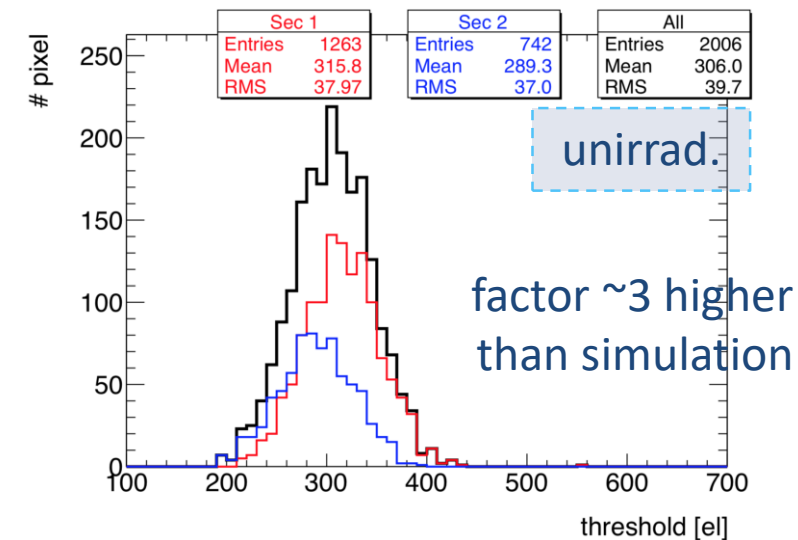


in-time threshold 130mV = 300 e<sup>-</sup>

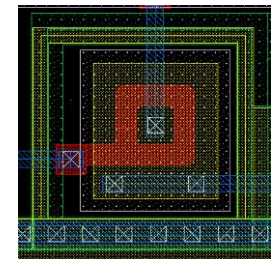
Time walk can also be obtained by measuring the delay of digital output signals with respect to a fast trigger (scintillator)

In-time efficiency for **leading signals** in clusters reaches **98%** with a 300 e<sup>-</sup> threshold (no correction for the **7.5 ns** propagation delay down the column)

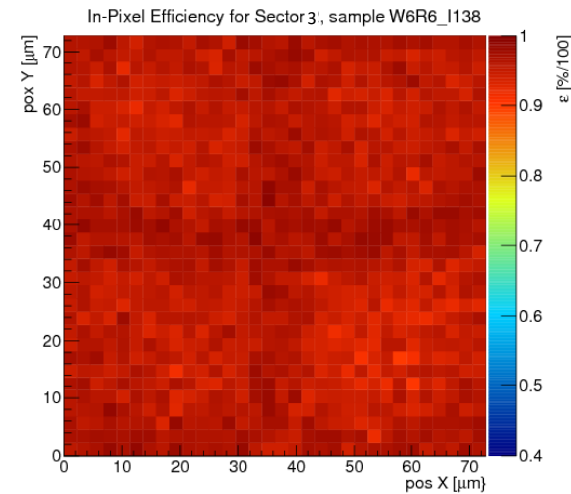
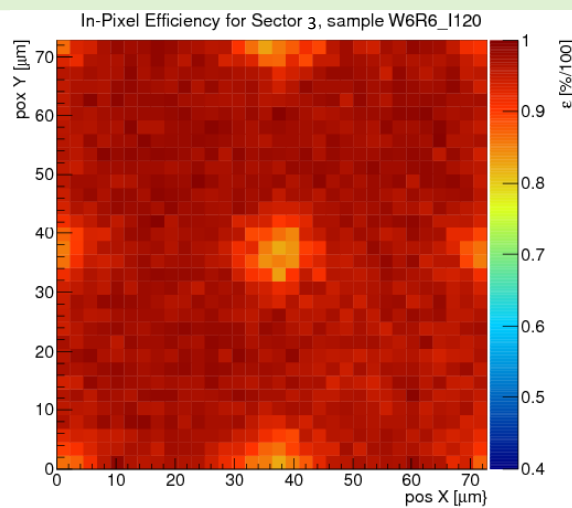
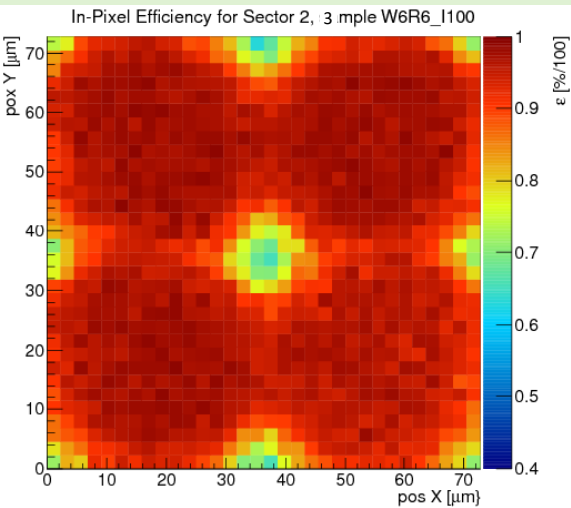




- Front-end still operational after 70 Mrad due to ELT in sensitive branch
- Increase in threshold spread and noise under investigation







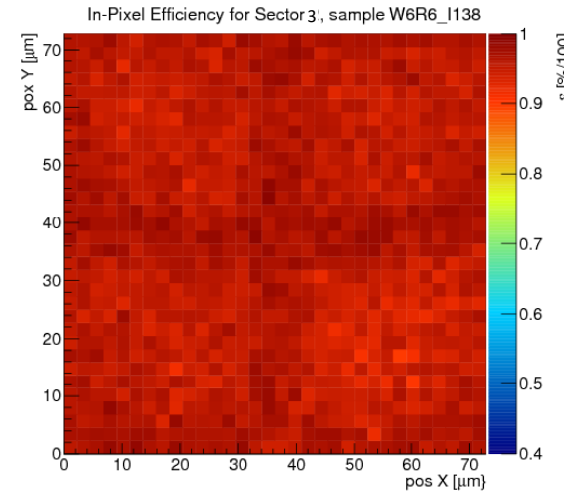
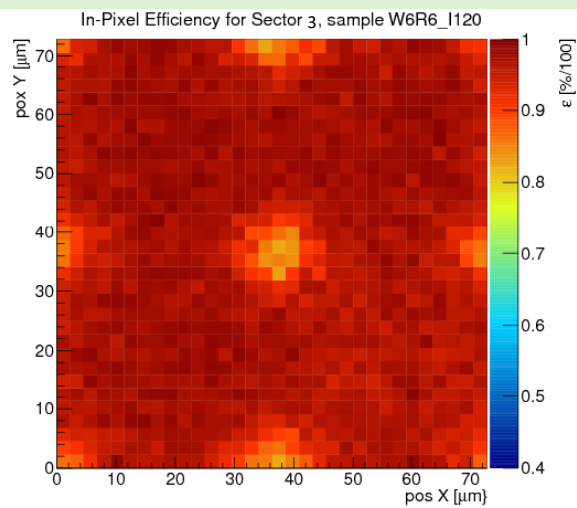
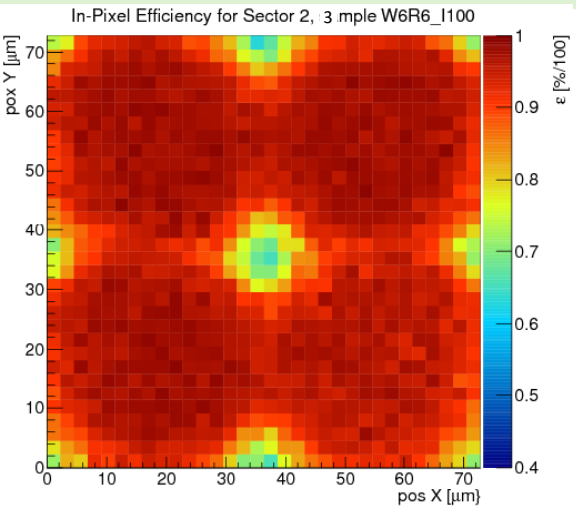
**Unirradiated:** lowering the threshold gives full efficiency

Decreasing threshold from  $\sim 600 e^-$  to  $\sim 250 e^-$  (unirrad.)

3

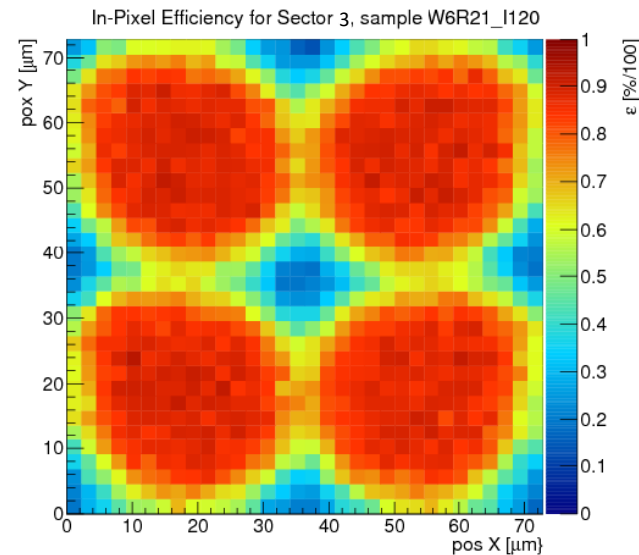
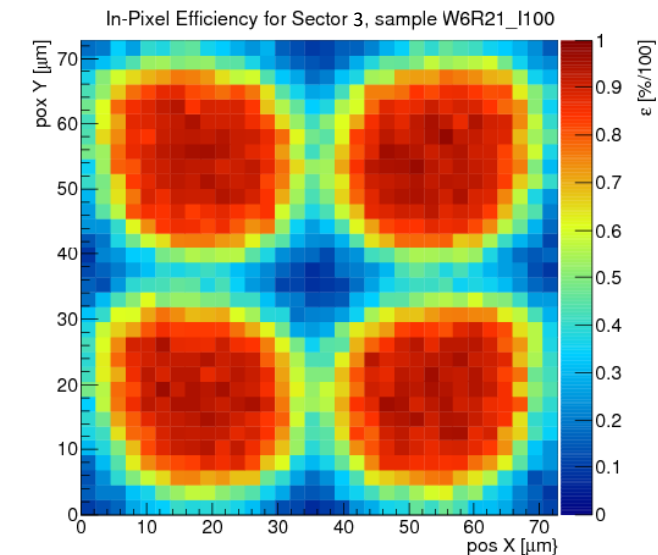
3

Cannot go lower with threshold because of RTS noise and masking issue  
Solution for both under study.



**Unirradiated:** lowering the threshold gives full efficiency

Decreasing threshold from  $\sim 600 e^-$  to  $\sim 250 e^-$  (unirrad.)/ $350 e^-$  (irrad.)

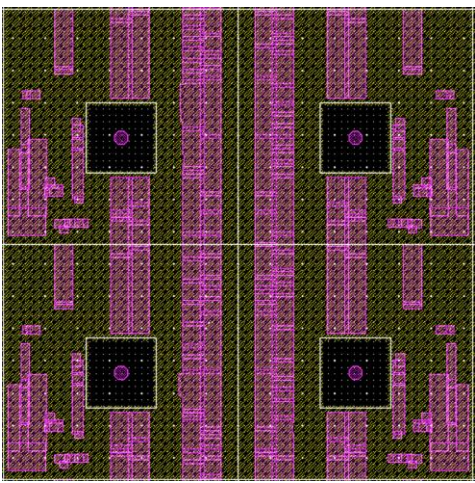
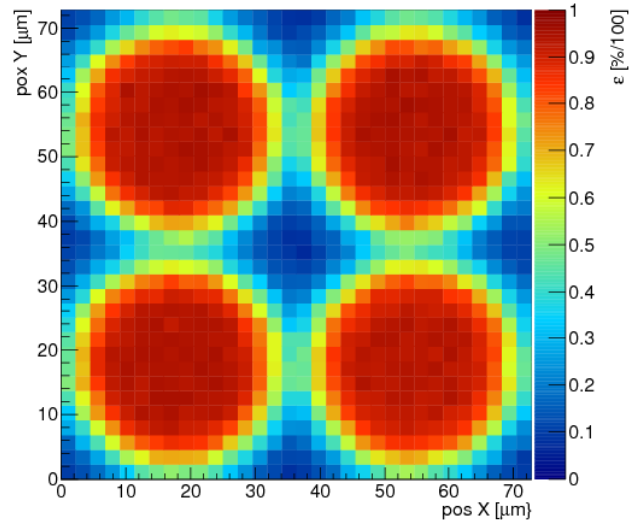


Could not reach lower threshold (RTS + MASKING ISSUE)

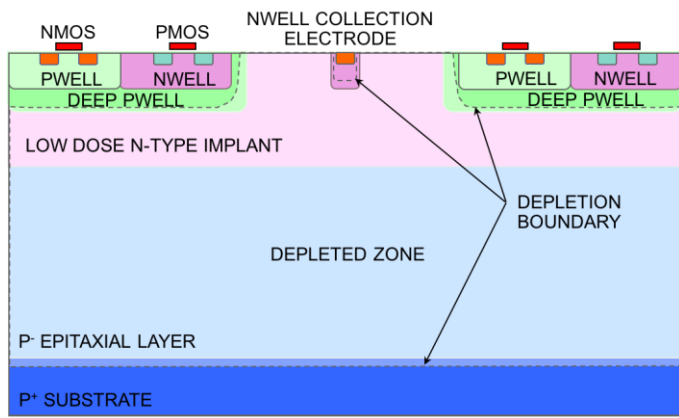
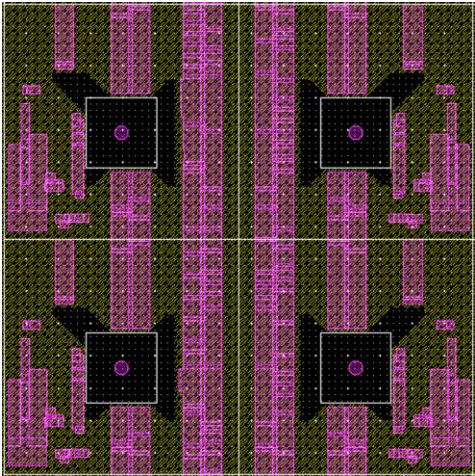
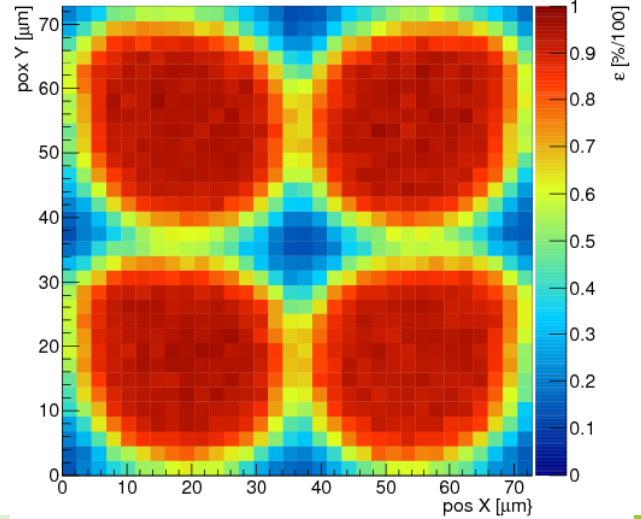
**Neutron irradiated**  
 $5 \times 10^{14} \text{ neq/cm}^2$   
 inefficiency in pixel corners due to low lateral electric field

# Efficiency vs. deep p-well coverage

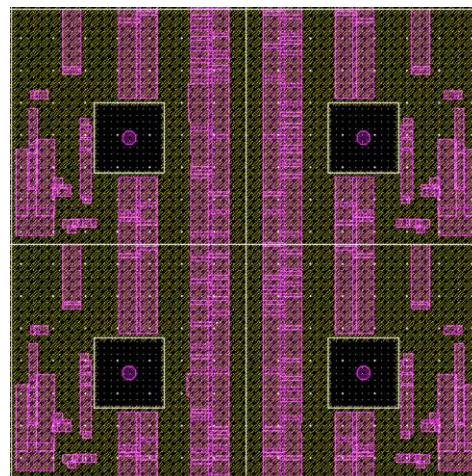
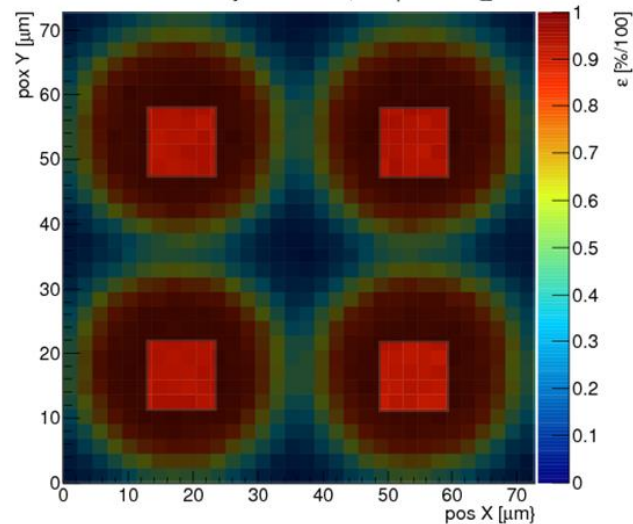
In-Pixel Efficiency for Sector 2, sample W4R2\_I130



In-Pixel Efficiency for Sector 2, sample W4R2\_I130

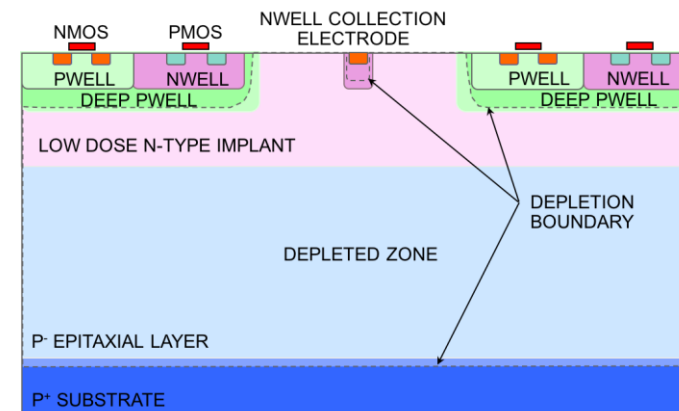
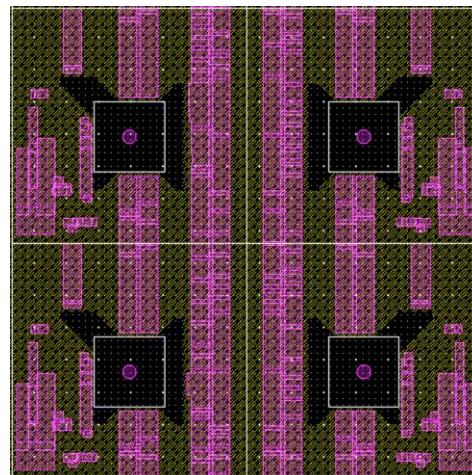
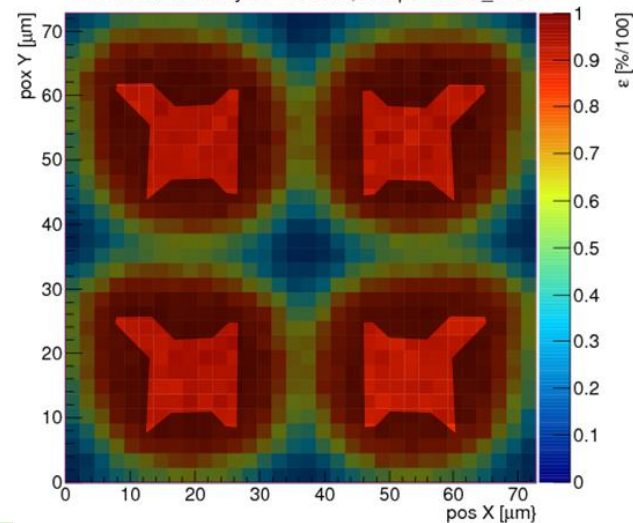


In-Pixel Efficiency for Sector 2, sample W4R2\_I130



- Deep p-well only needed under n-wells of PMOS transistors
- In-pixel efficiency can be correlated to deep p-well coverage around the collection electrode
- Removed deep p-well results in higher overall efficiency due to higher lateral electric field

In-Pixel Efficiency for Sector 2, sample W4R2\_I130



## Additional “extra-deep p-well” layer

- Already known by TowerJazz: no process R&D needed

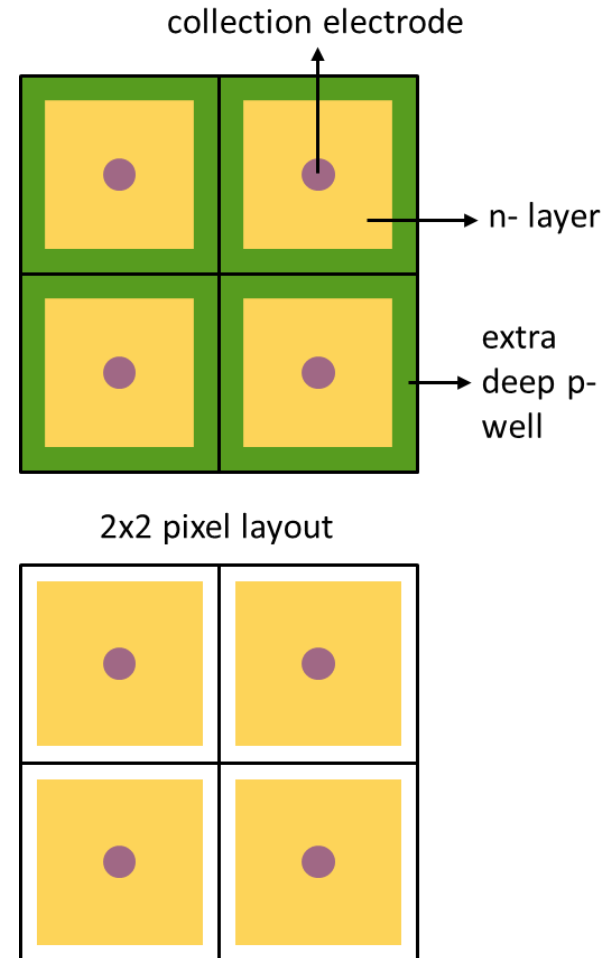
## Gap in the n- layer

- requires only a change of the existing mask for the n-layer

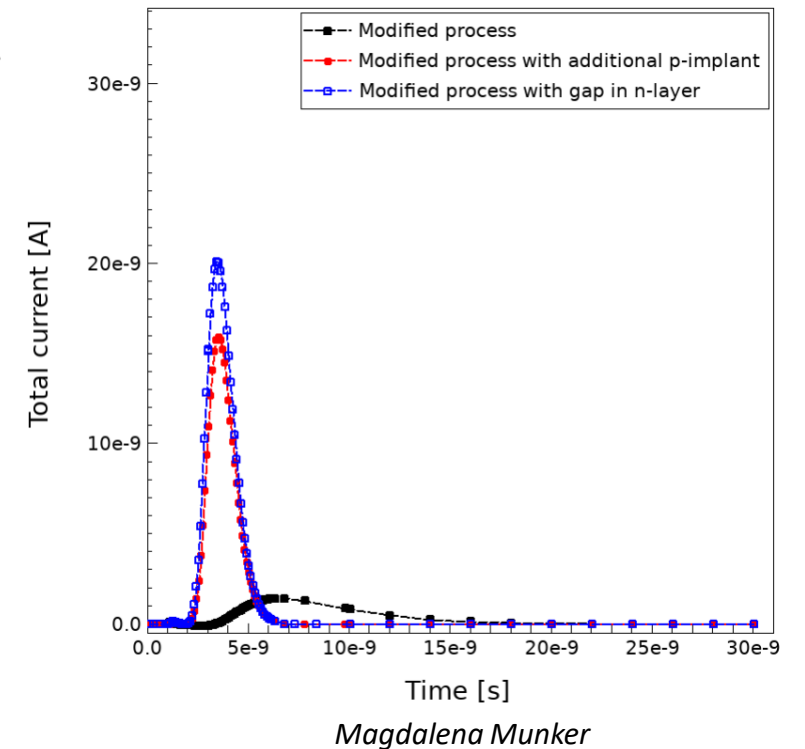
## Talk on efficiency simulations

Mon 10/12 11:10 Ruth Magdalena Munker

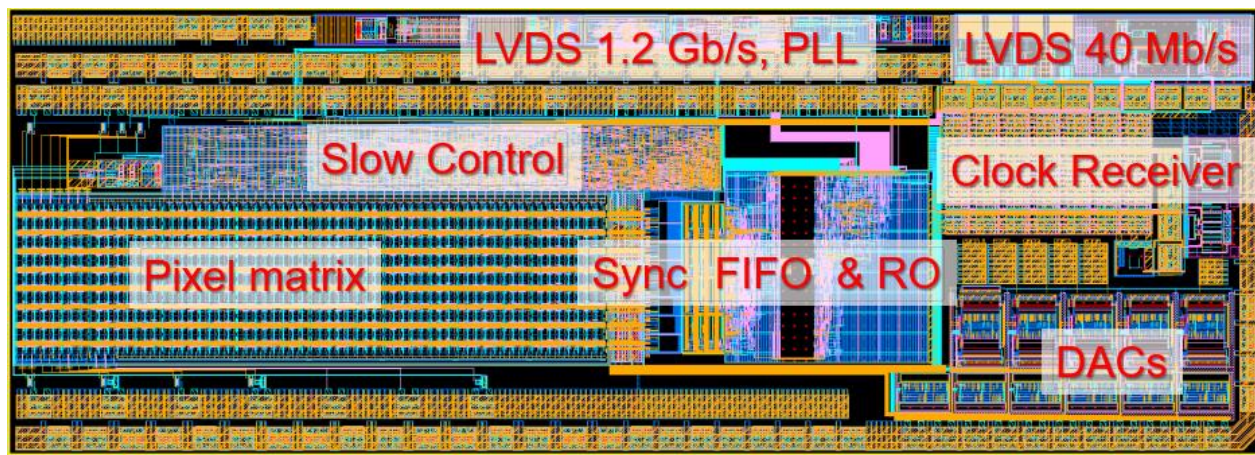
Simulations of CMOS sensors with a small collection electrode improved for a faster charge-collection and increased radiation tolerance



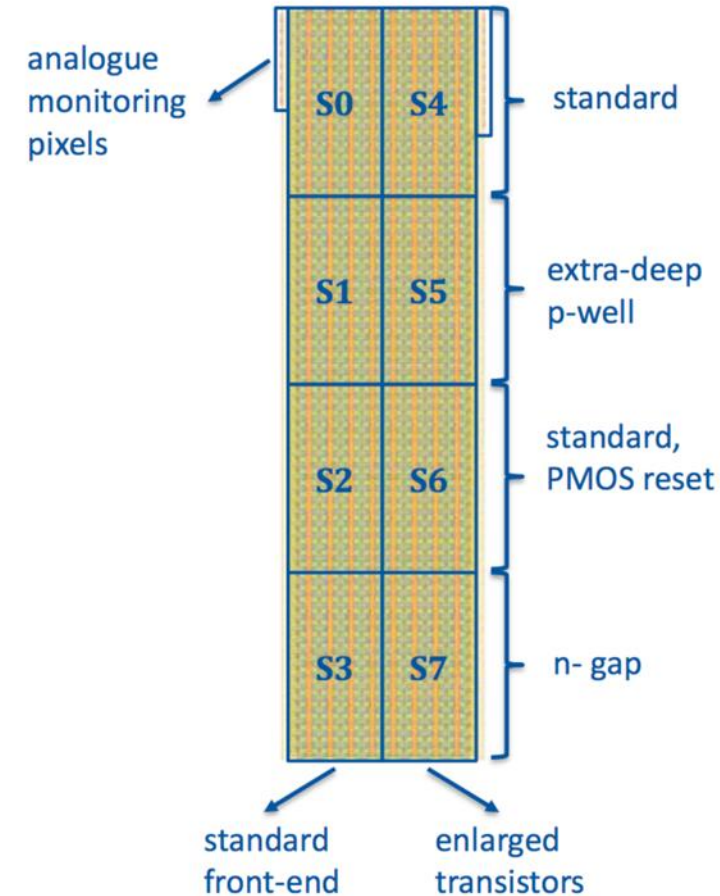
## After irradiation simulated current pulse



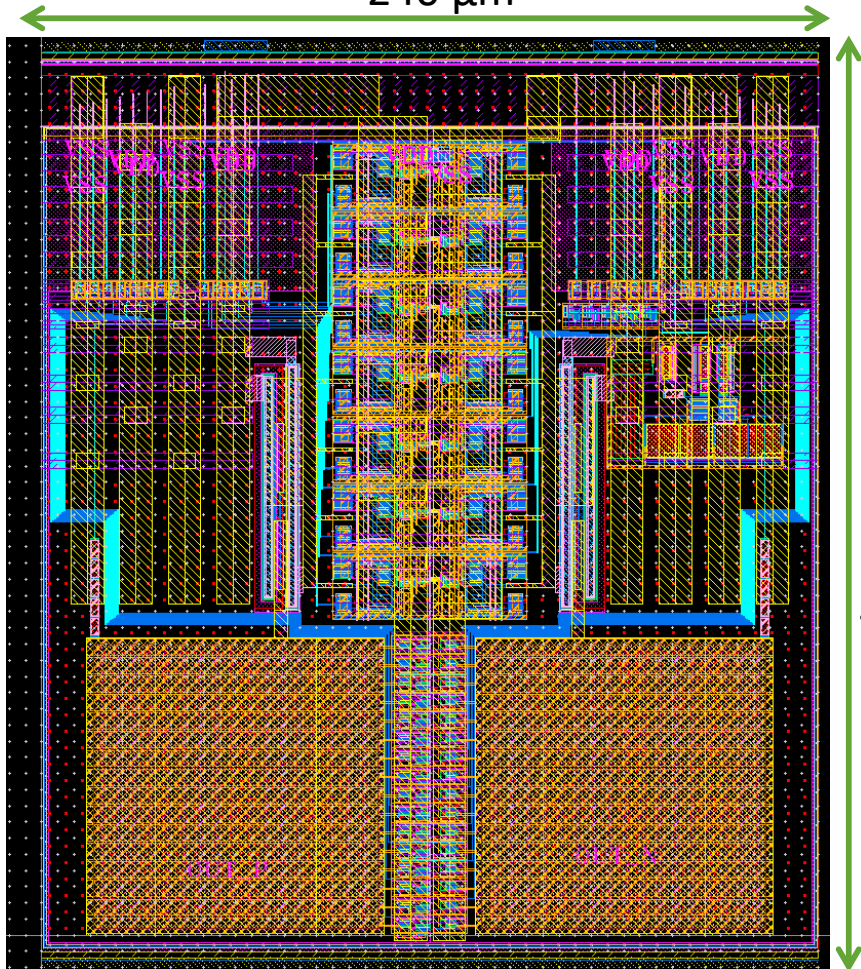
- Pixel size:  $36.4 \mu\text{m} \times 36.4 \mu\text{m}$
- 64x16 pixel matrix includes 8 sectors with splits on analogue front-end design, reset mechanism and process



Mini MALTA with synchronization and fixes for improved chargecollection



240  $\mu\text{m}$

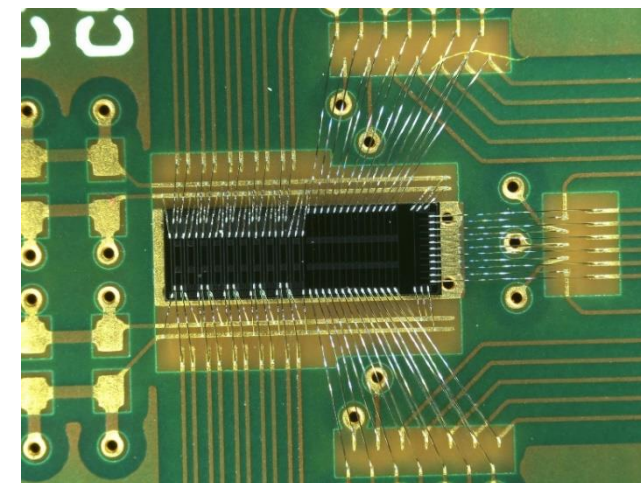


280  $\mu\text{m}$

5Gb/s

- 280 X 240 $\mu\text{m}^2$  (2 pad pixel pitch)
- Tunable DC current (7x 0.8mA )
- Modular capacitive coupled pre-emphasis: 16 blocks driving 25fF each.
- Vcm feedback control at 0.8V.
- External 100  $\Omega$  differential termination
- 40 drivers integrated in MALTA (up to 2Gb/s)

Dedicated testchip



5Gb/s

1.28Gb/s (ITk specification)



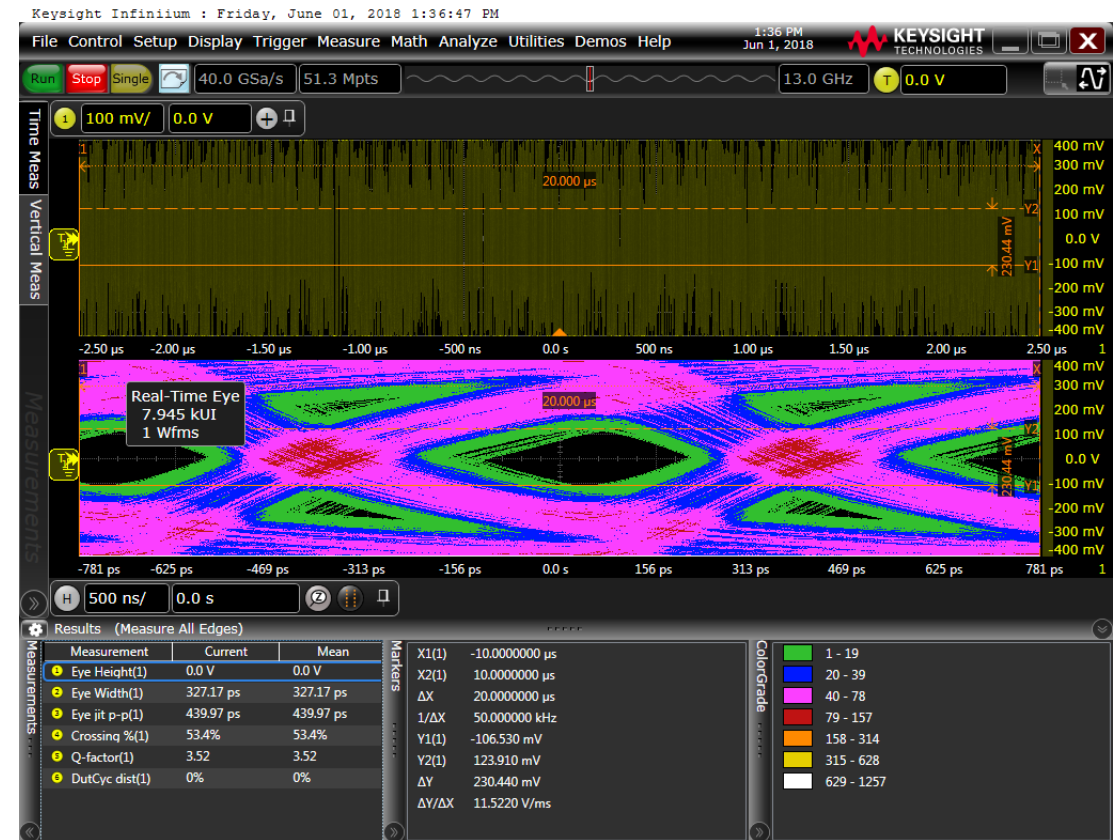
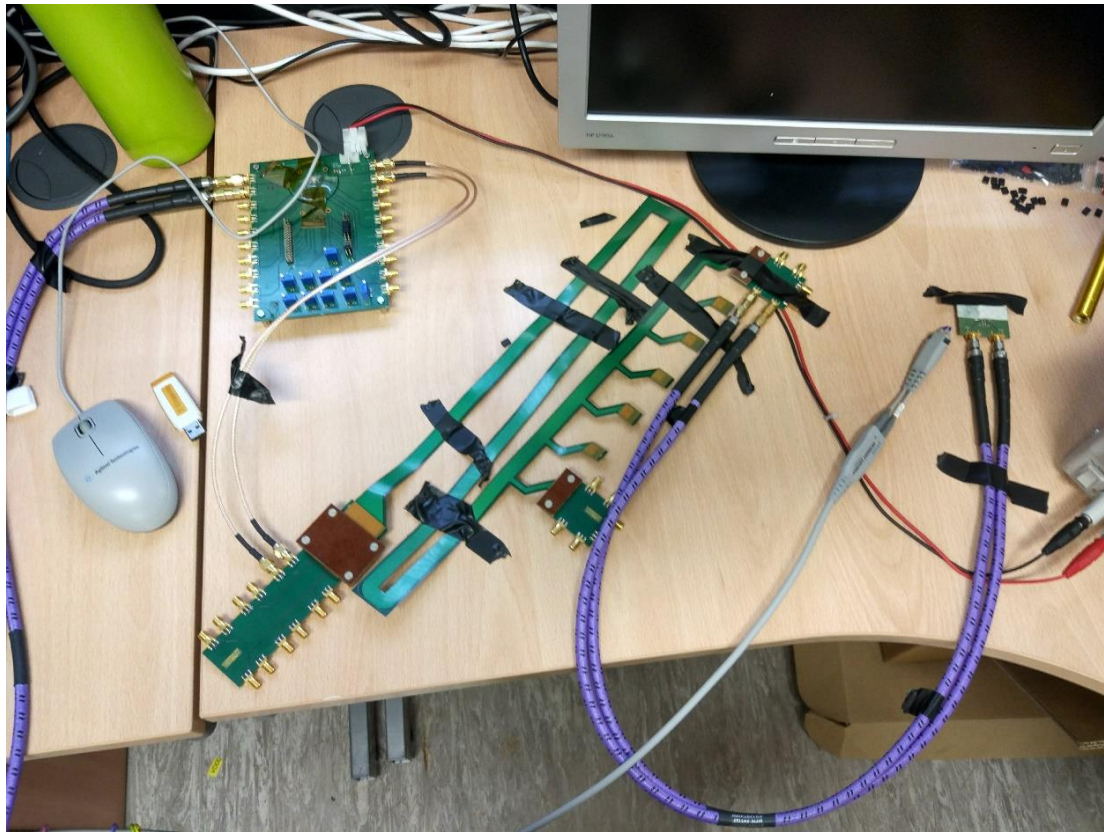
Jitter<sub>p-p</sub> = 71ps



Jitter<sub>p-p</sub> = 38ps



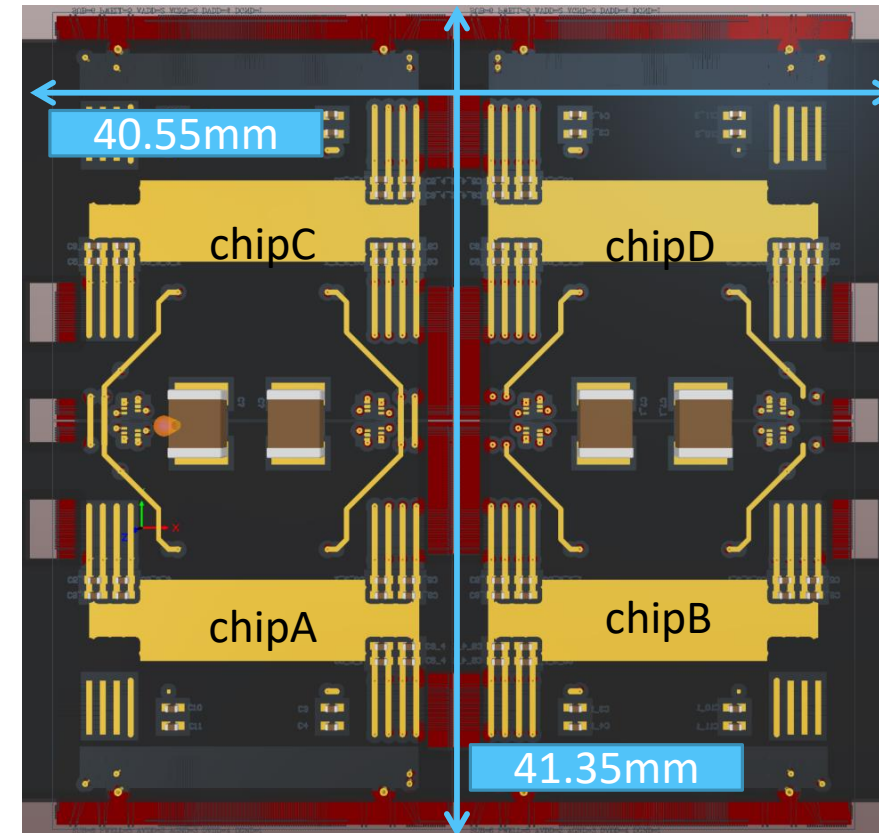
Flex for data transmission out of the ITk system (length~5m)



The ATLAS ITk sensors will be organized in quad modules.

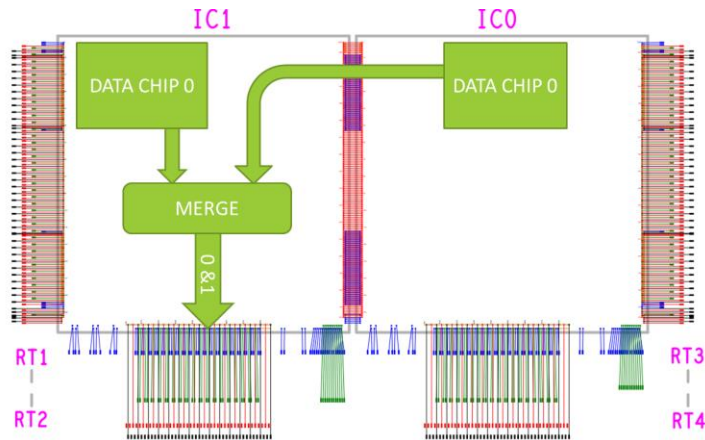
In the case of the hybrid pixel, one sensor of around  $4 \times 4 \text{ cm}^2$  will be bonded to four  $2 \times 2 \text{ cm}^2$  front-end chips

MALTA is the first large scale monolithic chip that allow build a compatible Quad-Module, assembling four detectors in a single FLEX



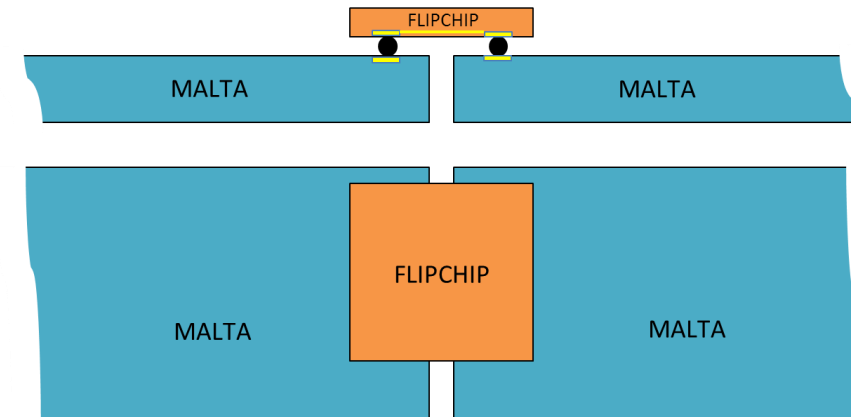
Under design

## Chip to Chip communication



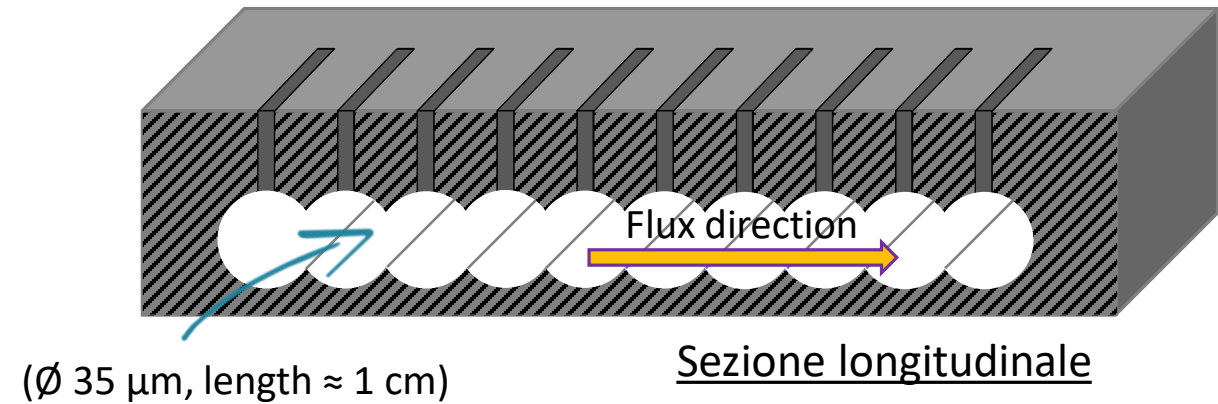
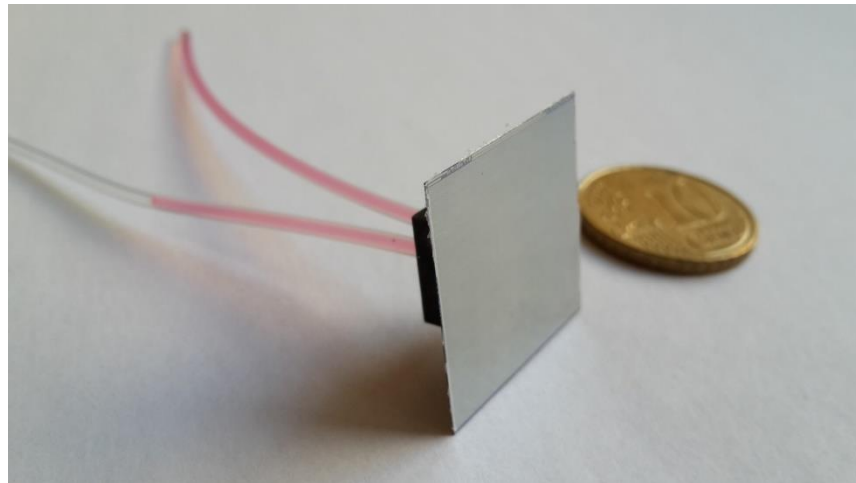
MALTA can transmit power and data asynchronously to a neighboring chip (via CMOS pad), merging the data of multiple pixel matrix in just one parallel output

## Flip chip connection



Connection between neighboring chips using flip chip

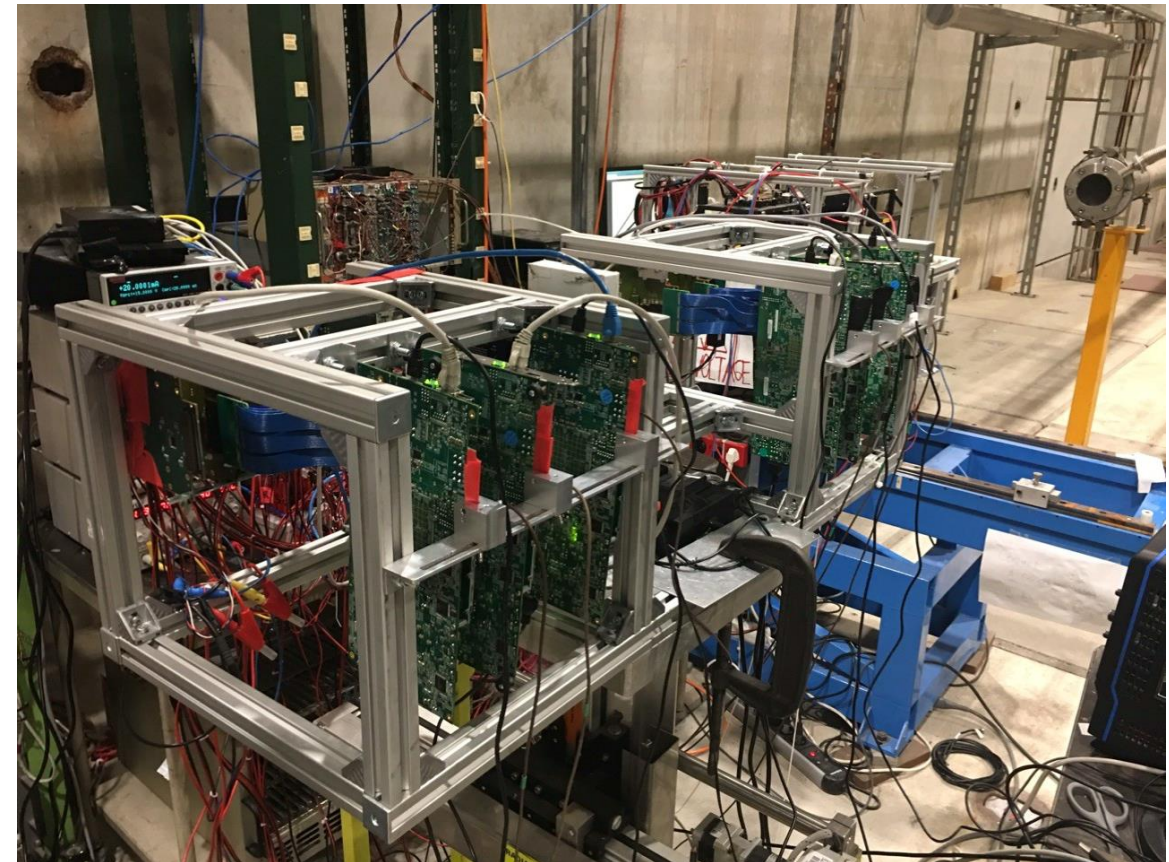
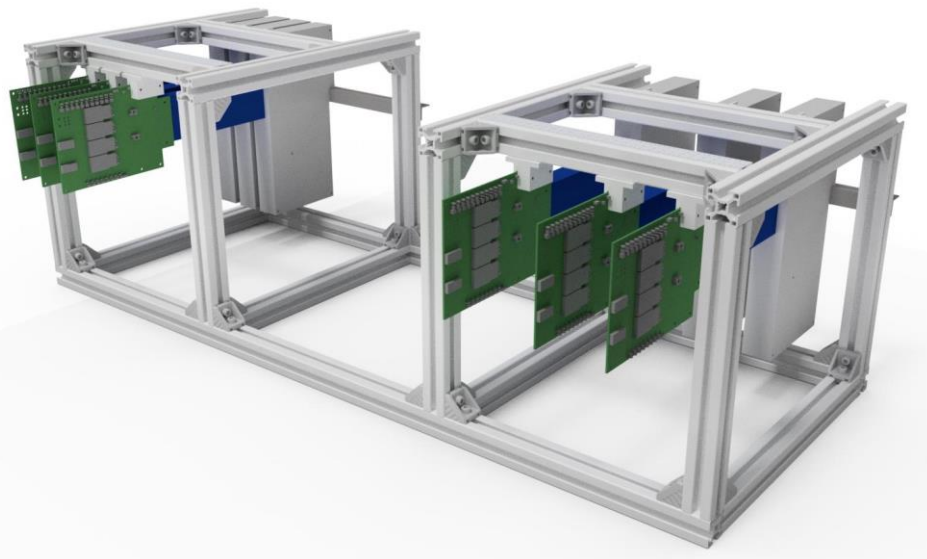
- Better for assembling
- Allow additional electronics in the flipchip



DOI: [10.1109/ITHERM.2012.6231493](https://doi.org/10.1109/ITHERM.2012.6231493)

J. Bronuzzi, A. Mapelli, R. Callegari, P. Riedler

6 MALTA chip-based planes  
 2 Scintillators  
 4um resolution



The MALTA CMOS pixel sensor was developed in view of the ATLAS High-Luminosity upgrade.

The large pixel matrix implements a fast, low-power analogue front-end and a novel asynchronous readout architecture.

The chip has been extensively characterised in lab measurements and testbeam, and shows promising results in terms of front-end performance and readout capability, but needs further improvement:

The small collection electrode sensor suffers from degraded efficiency in the pixel corners after irradiation to  $10^{15}$  neq/cm<sup>2</sup>, and this is being addressed by means of improvements in the process (see M. Munker's presentation), and also in the front end design to obtain a lower threshold.

An LVDS driver has been designed and tested to transmit the data to the ITk readout system, up to 5Gb/s.

The MALTA chip allows to build the first prototype of a monolithic module, compatible with the hybrid equivalent for the ITk system.

Several R&D on monolithic pixel sensors are in progress using the MALTA chip, such as buried channels cooling and chip to chip data communication.

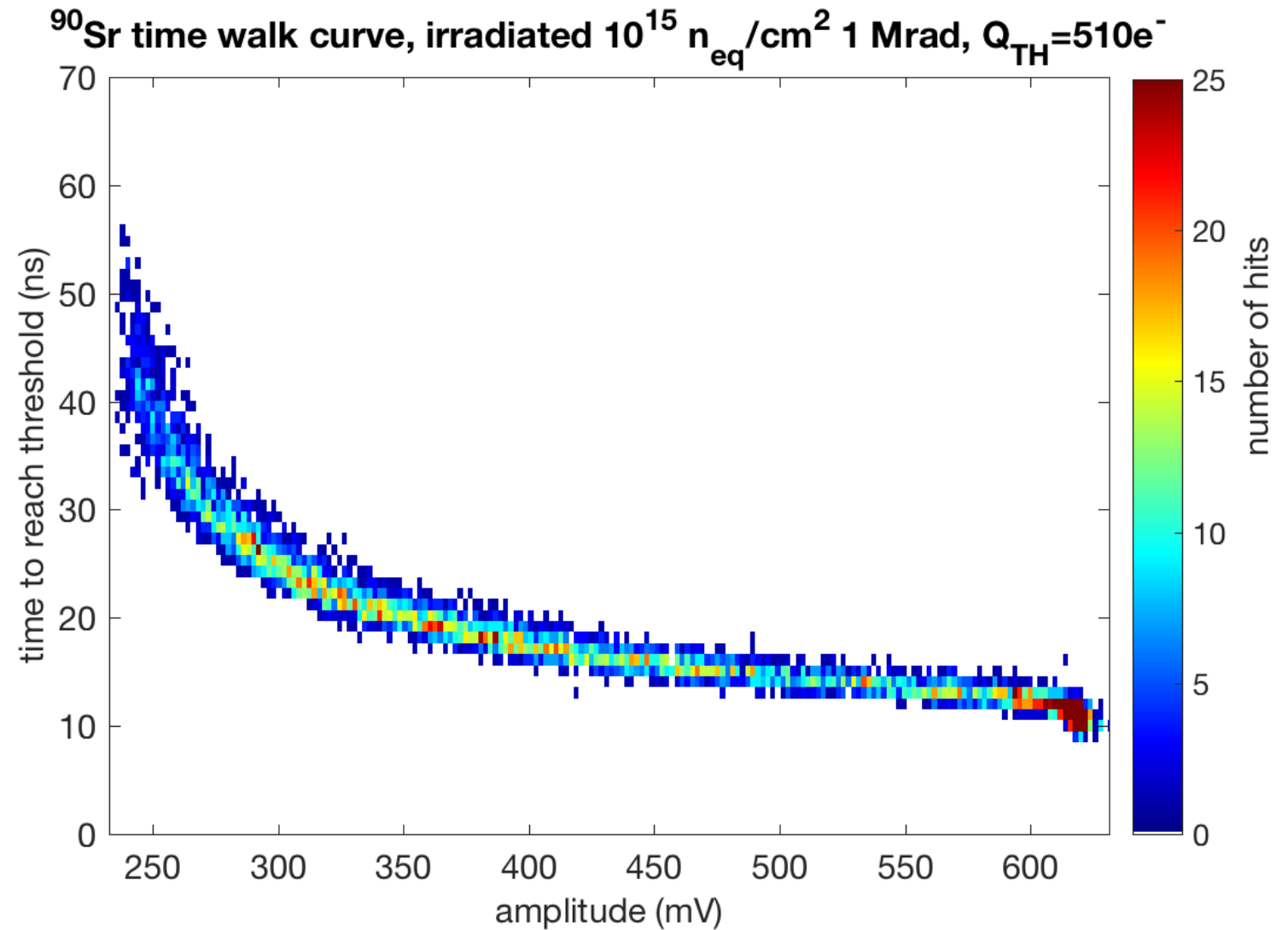
# Thank you for the attention

## Question time!

# Backup slides

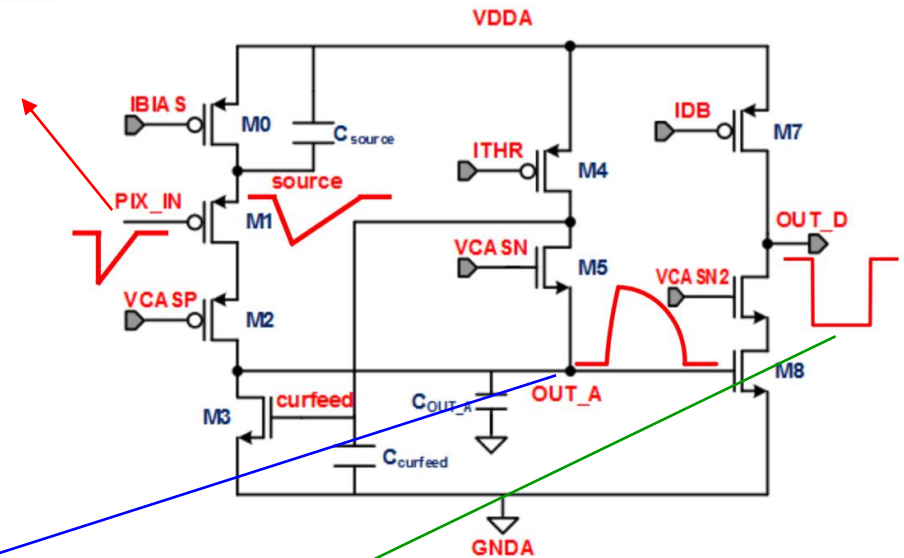
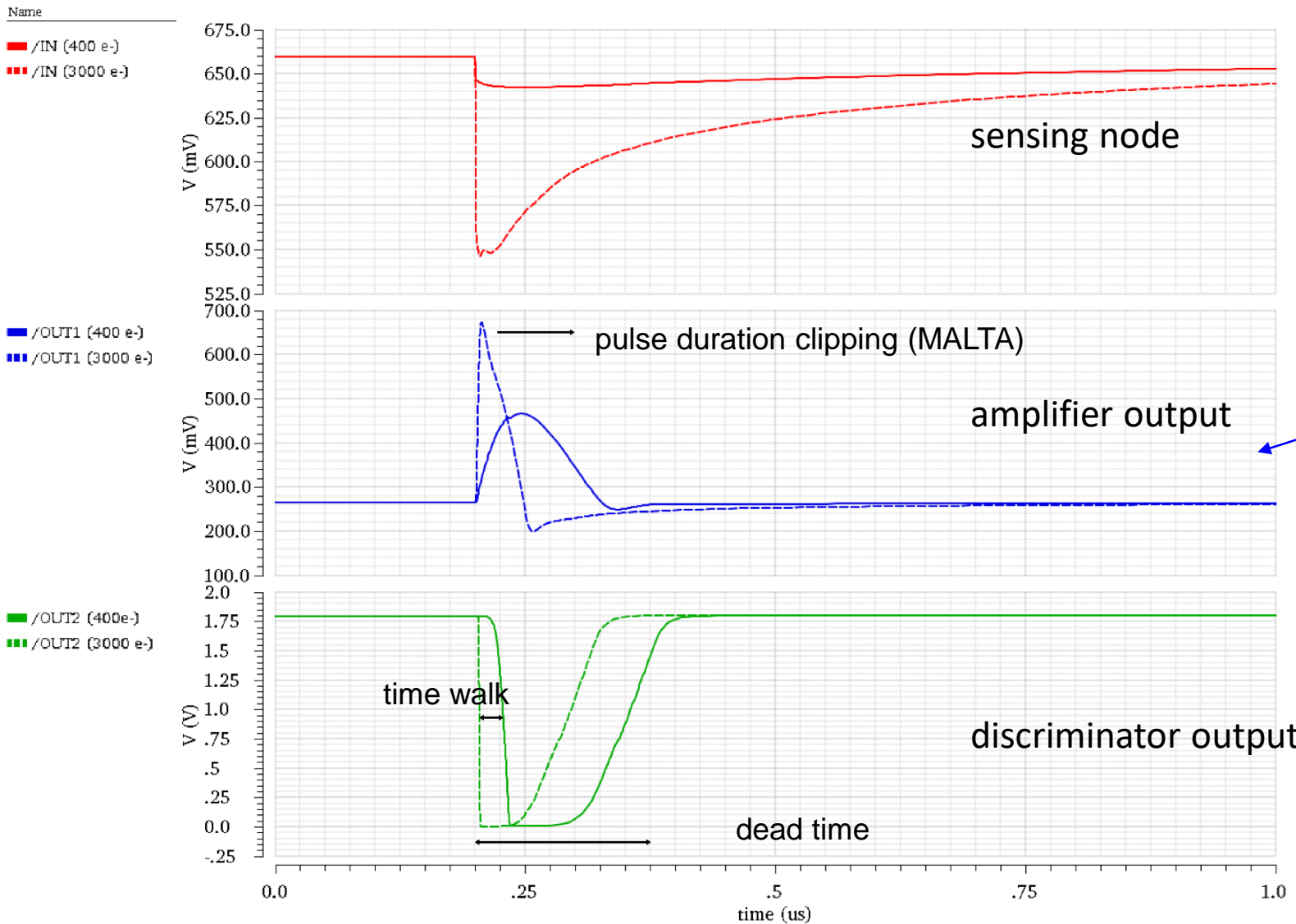


Little change in front-end signal and timing after irradiation (somewhat more charge sharing)



# Front-end optimization (simulation)

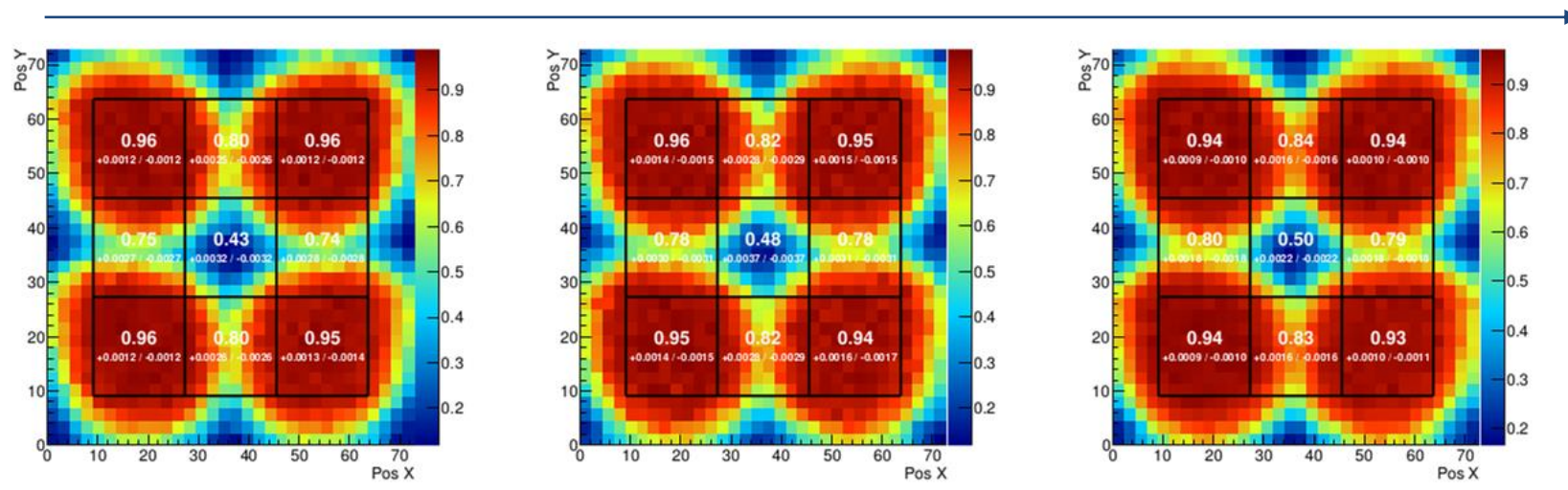
I. Berdalovic et al 2018 JINST 13 C01023



$$P_{\text{analog}} = 0.9 \mu\text{W}$$

Charge threshold $Q_{\text{th}}$	300 e
Equivalent Noise Charge	7.1 e
Channel-to-channel RMS	10.2 e

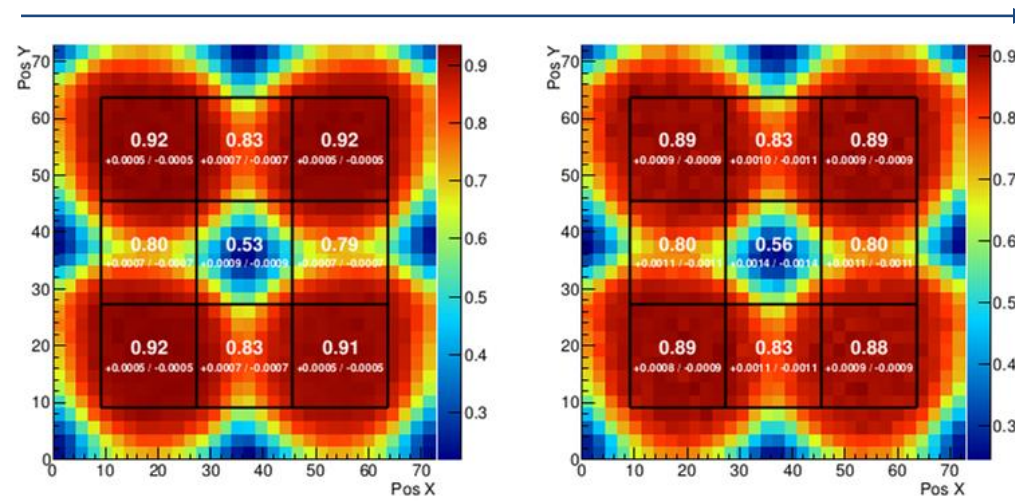
# Efficiency after irradiation to $10^{15} n_{eq}/cm^2$



(a)

(b)

(c) Decreasing threshold from  $\sim 450 e^-$  to  $\sim 350 e^-$



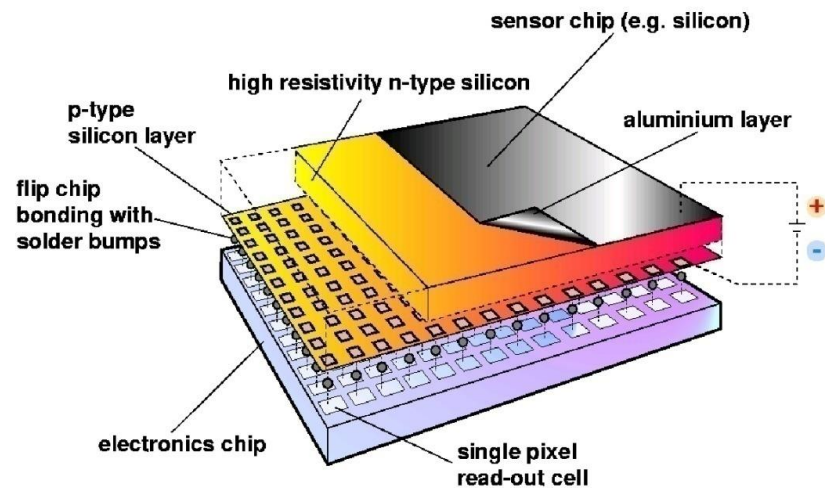
(d)

(e)

Artifact: pixel center efficiency decreases at low thresholds due to noise issues

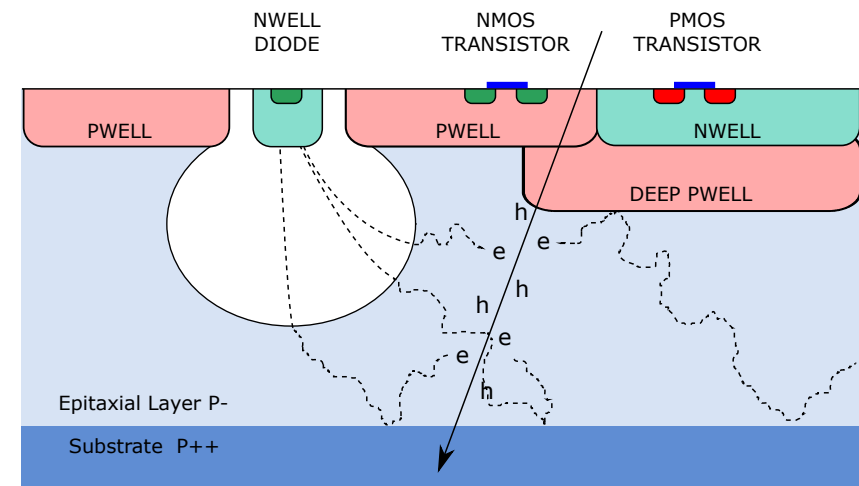
## Hybrid

- Used in current LHC detectors
- Optimized silicon sensor for radiation hardness
- Dedicated front-end electronics bonded to the sensor
- Thick modules
- Complex and costly assembly due to fine-pitch bump bonding



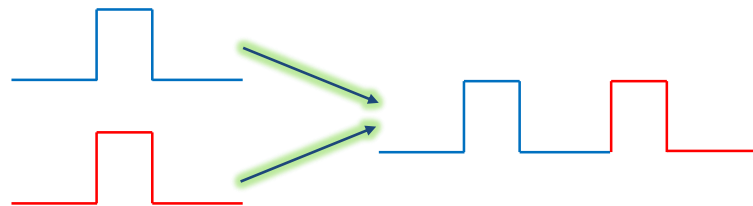
## Monolithic

- Promising technology for future detectors
- Single chip integrate electronic and sensor
- Radiation hardness limitation
- Lower material budget
- Large number of available vendors



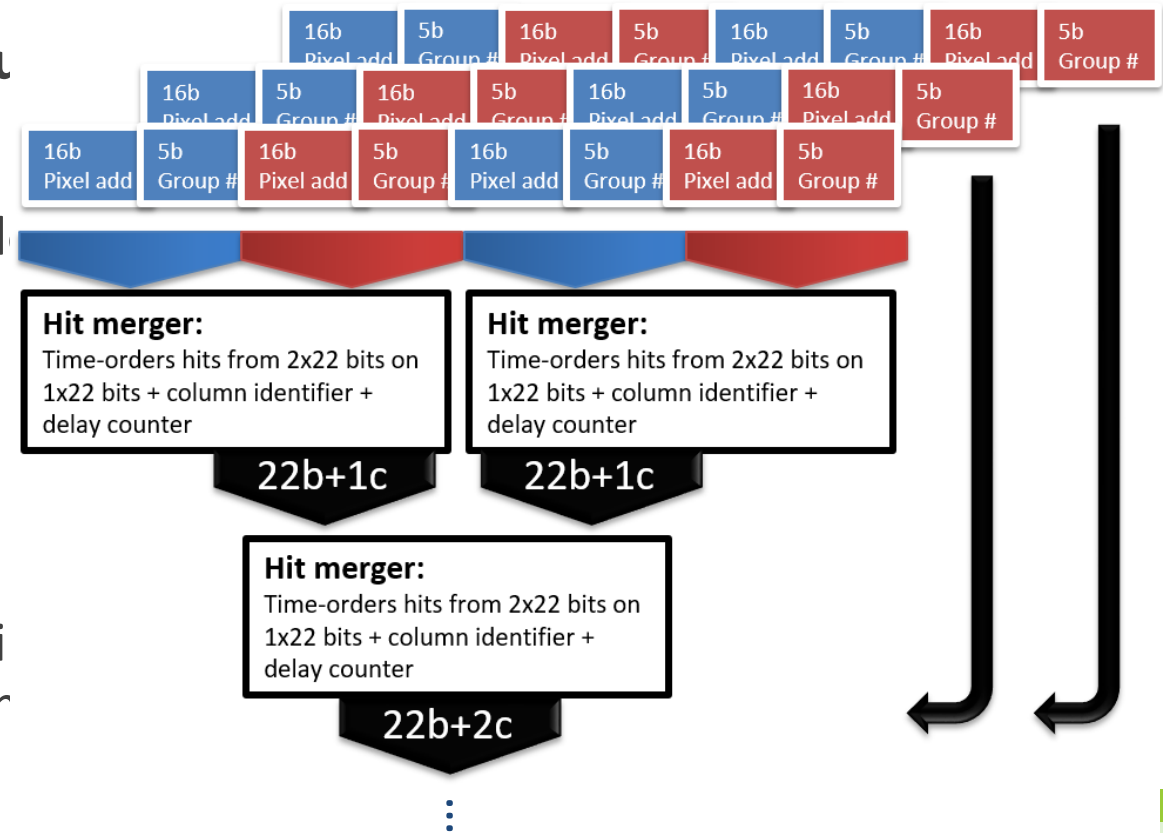
The MALTA periphery implements a fully **asynchronous** signals coming from groups with different colour

In the case of simultaneous signals on two buses the l the other is delayed



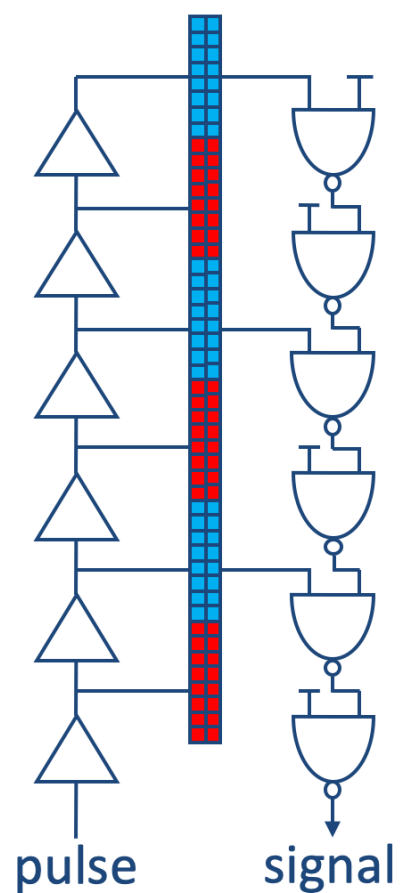
Merging is repeated for all the double-columns in a bi column address bit in each step, until all outputs are r bus

x256 double-columns  
⋮

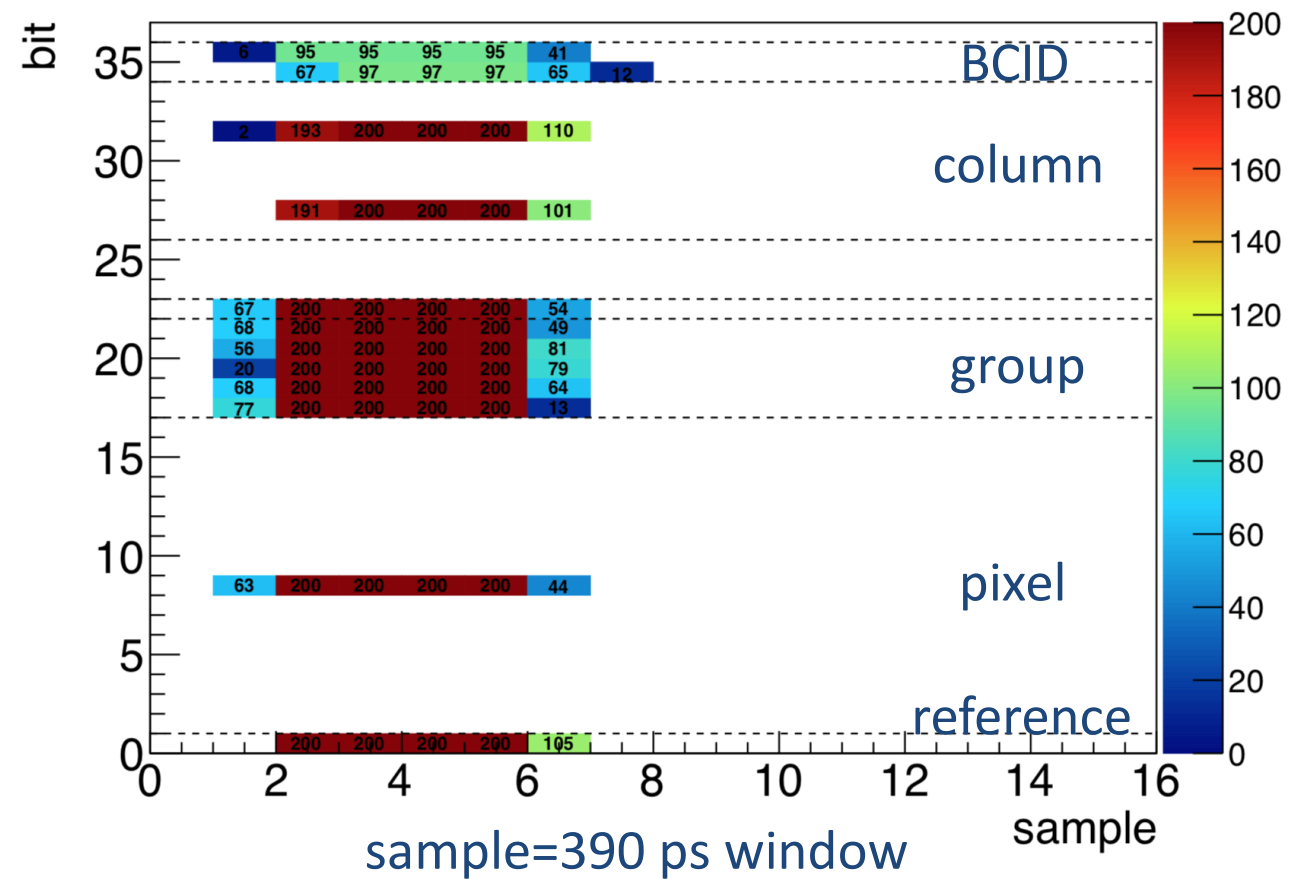


⋮  
x10 levels of merging for full matrix

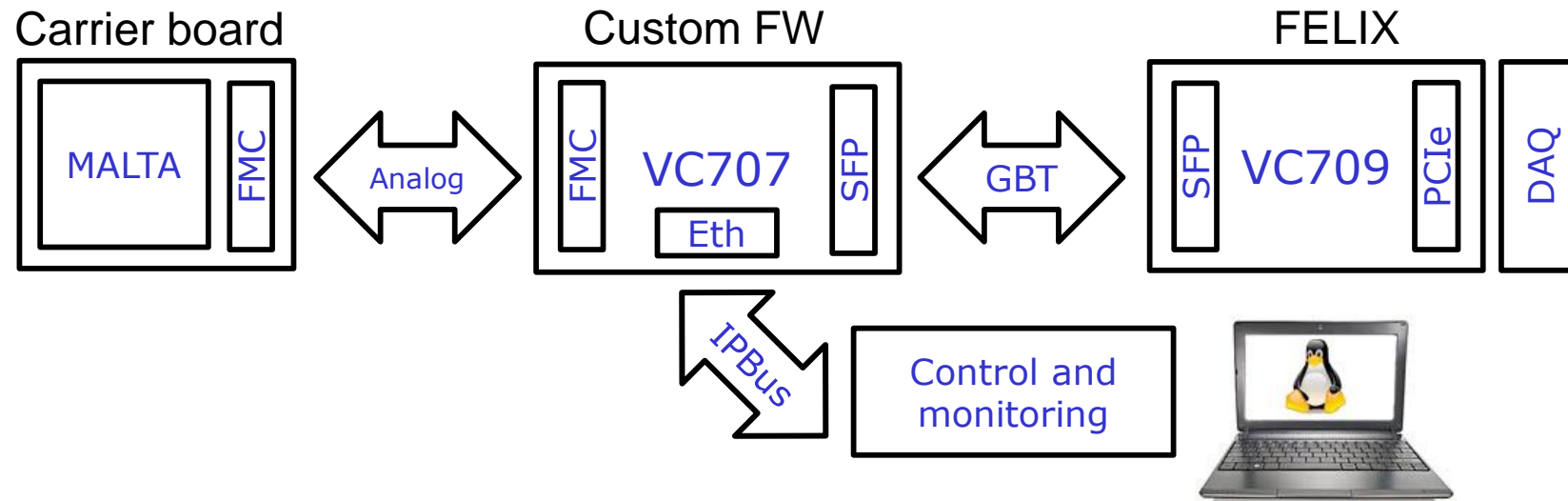
Parallel data bus requires **delay uniformity**: all at the reference signal



(pulsing a pixel 200 times and oversampling the output signals to check the timing alignment)



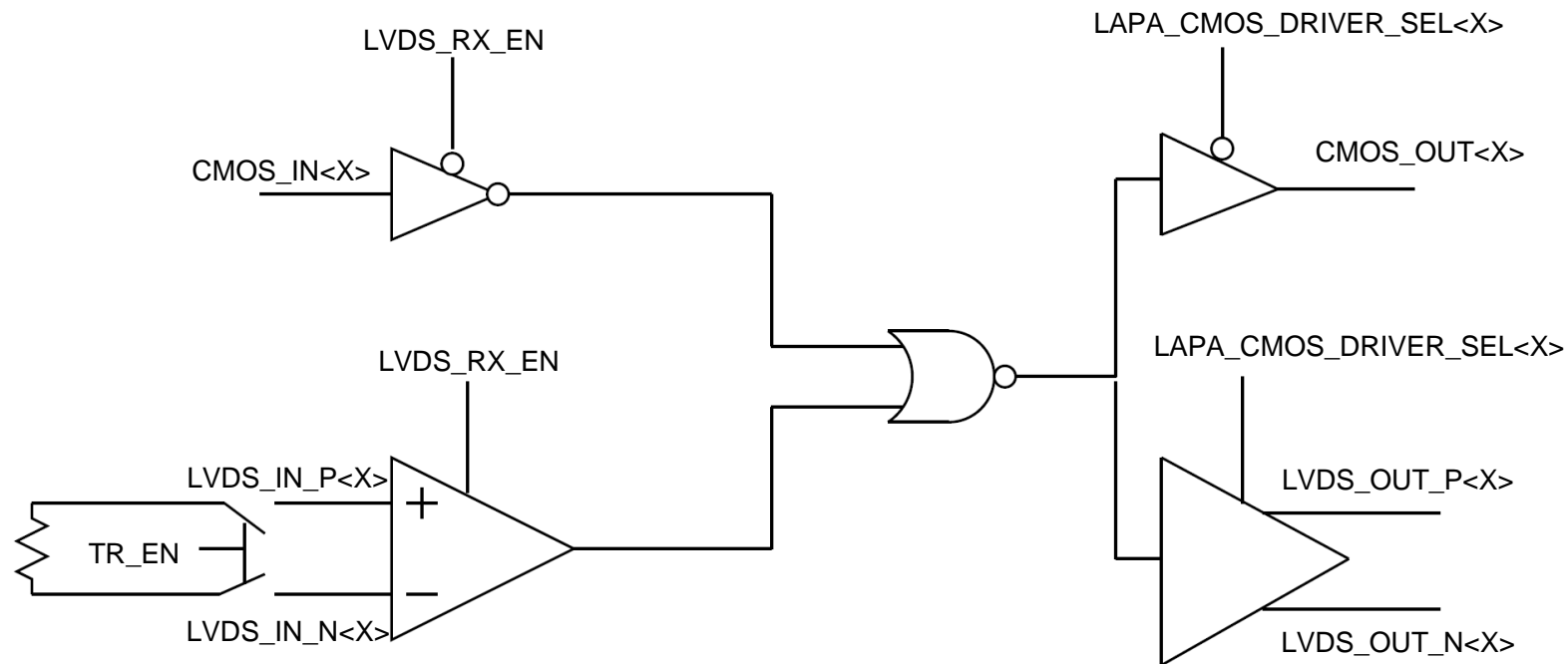
sample=390 ps window



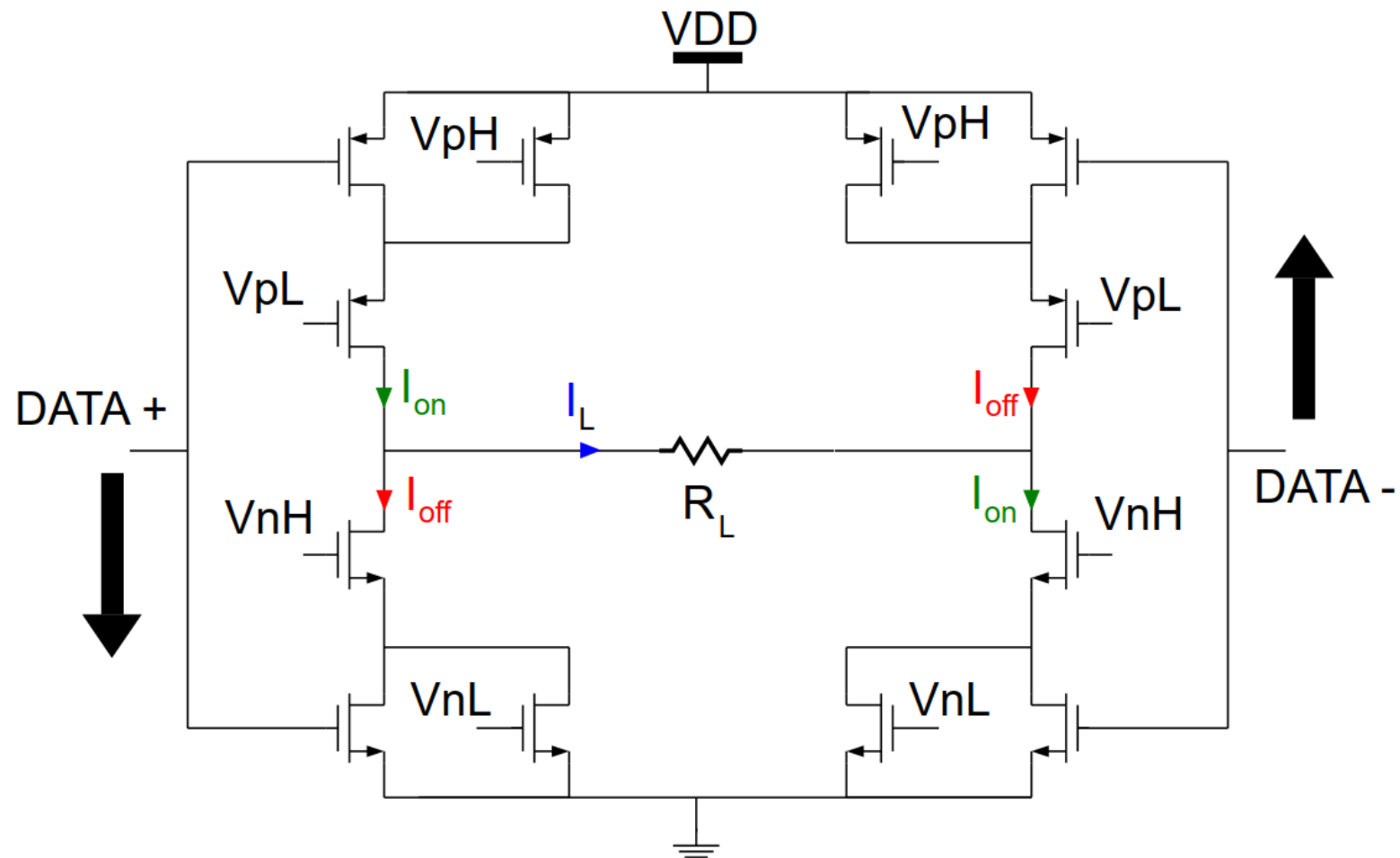
- Carrier board for two MALTA chips with FMC interface
- Asynchronous oversampling on Xilinx VC707 board
- Slow read-out through IPbus ethernet to Linux PC running SLC6
- Fast read-out through GBT optical link with FELIX + ITK SW

R. Cardella, V. Dao, C. Marin Tobon, E.J.Schioppa, B. Schlager, L. Simon Argemi, C. Solans Sanchez

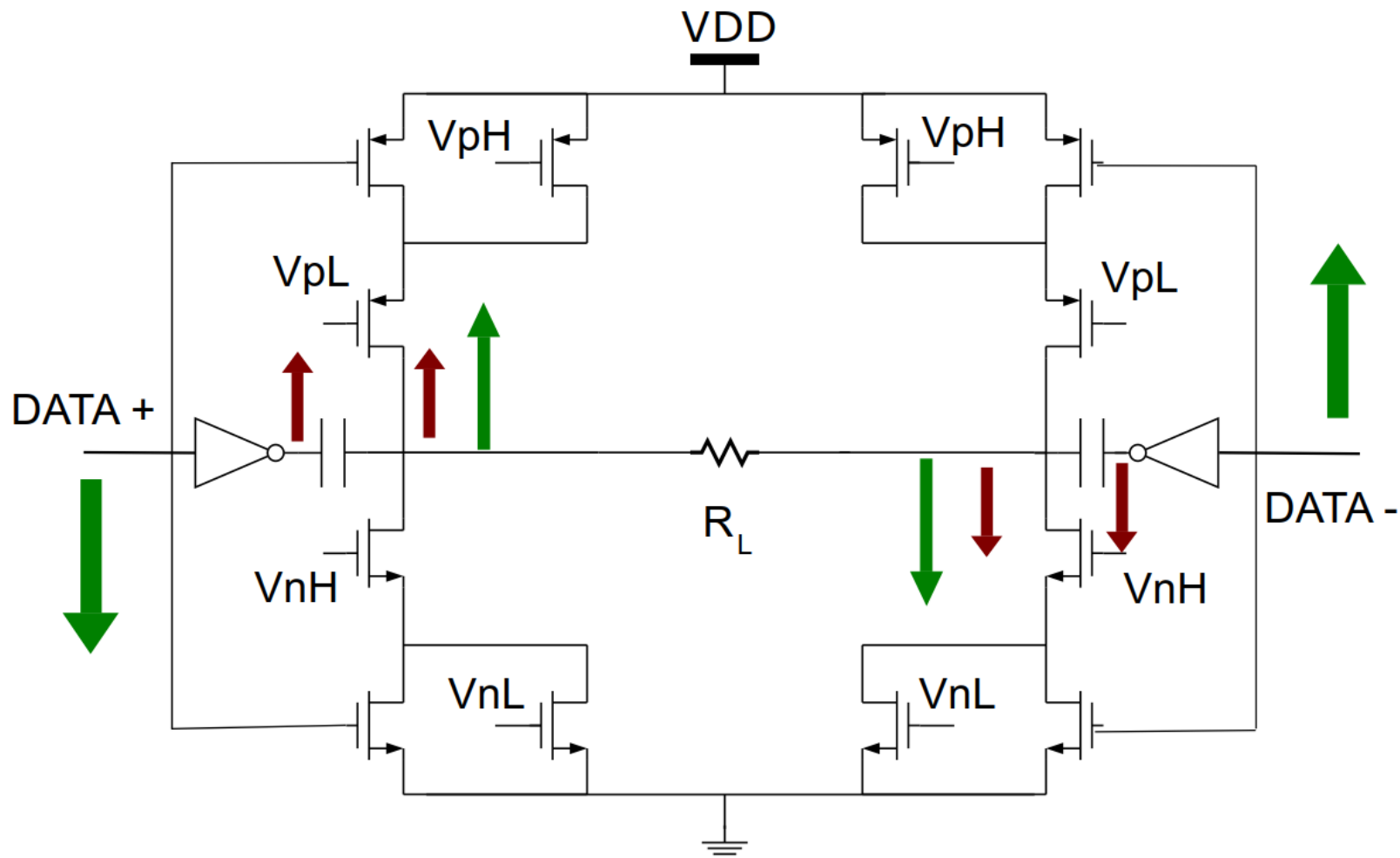
# LAPA Single Channel Schema



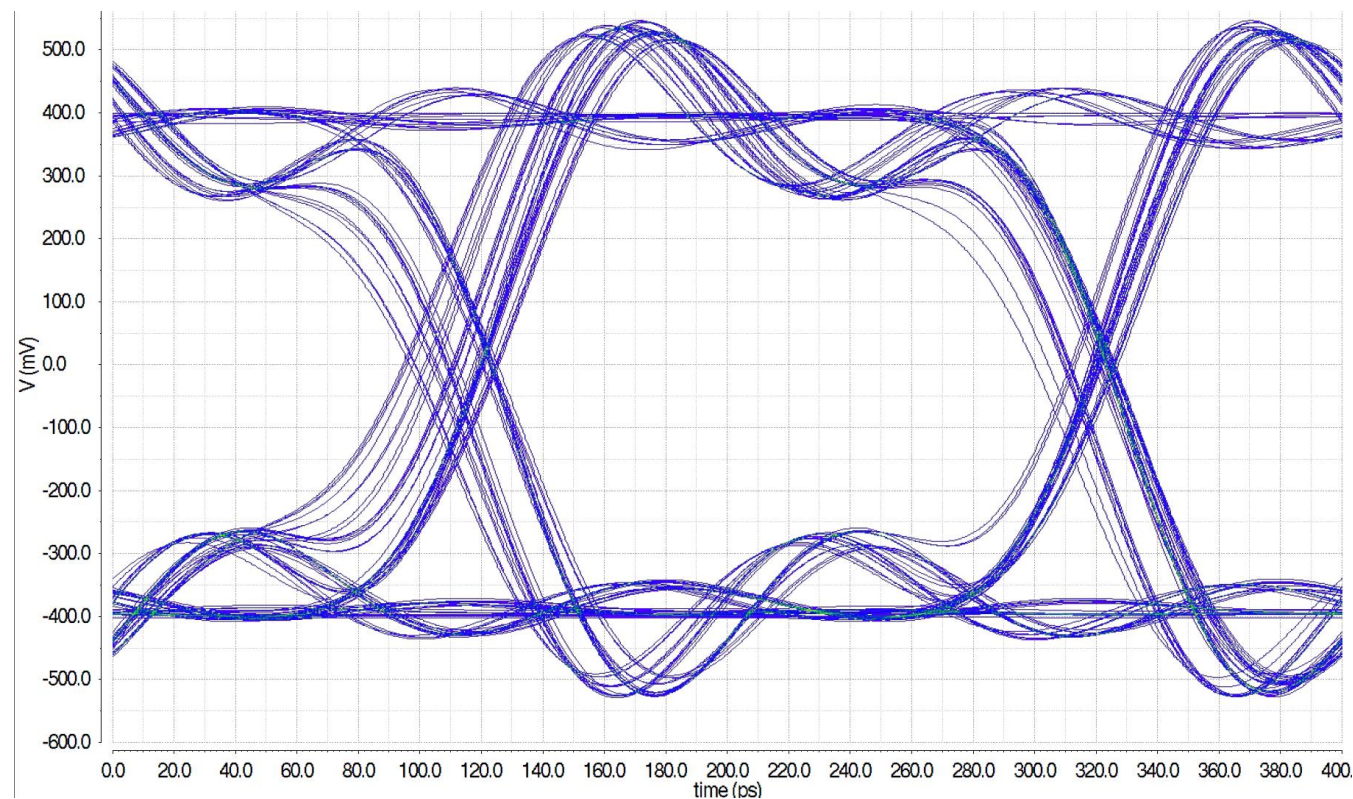




**7 HBRIDGE blocks of 0.8mA - max: total 6mA**



**16 BLOCKS driving 25fF coupled with the output pad**



**2.5GHz LVDS IN – LVDS OUT. 100Ω termination. 1pF load.**

**Simulated jitter=45ps**

## Preliminary power consumption

### Expected static power consumption

Static	Current [mA]	Power [mW]
5 Hbridge	4	7.2
7 Hbridge	5.2	10

### Measurements on test chip

Static+Dynamic 1.28Gb/s	Current [mA]	Power [mW]
5 Hbridge	6	10.8
7 Hbridge	8	14.4

